FABRICATION AND STUDY OF MOLECULAR DEVICES AND PHOTOVOLTAIC DEVICES BY METAL/DIELECTRIC/METAL STRUCTURES

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ABSTRACT OF DISSERTATION

Bing Hu

College of Engineering
University of Kentucky
2011
FABRICATION AND STUDY OF MOLECULAR DEVICES AND PHOTOVOLTAIC DEVICES BY METAL/DIELECTRIC/METAL STRUCTURES

ABSTRACT OF DISERTATION

A dissertation submitted in partial fulfillment of the requirements for the degree of Doctor of Philosophy in the College of Engineering at the University of Kentucky

By

Bing Hu

Lexington, Kentucky

Director: Dr. Bruce J. Hinds, Professor of Materials Engineering

Lexington, Kentucky

2011

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ABSTRACT OF DISSERTATION

FABRICATION AND STUDY OF MOLECULAR DEVICES AND PHOTOVOLTAIC DEVICES BY METAL/DIELECTRIC/METAL STRUCTURES

A new class of electrodes with nanometer-scale contact spacing can be produced at the edge of patterned metal/insulator/metal this film structures. A key challenge is to produce insulator layers with low leakage current and have pristine metal contacts for controlled molecular contacts. Atomic layer deposition of high quality Al₂O₃ thin films onto Au electrodes was enabled by surface modification with a self-assembled monolayer of -OH groups that react with a monolayer of trimethylaluminum gas source. Ar ion milling was then used to expose the edge of the Au/dielectric/Au structure for molecular electrode contacts. The junctions are characterized by atomic force microscope and tunnel current properties. The Au/self-assembled monolayer/Al₂O₃/Au tunnel junction, with a very thin oxide insulator layer (15.4 Å), is stable and has a small tunneling current density of about 0.20 ~ 0.75 A/cm² at 0.5 V. Organometallic cluster molecules were attached to bridge the electrodes. Through tunnel current modeling, low temperature and photo current measurements, molecular current was found to be consistent with direct tunneling through the organic tethers to available states at the metal center.

This novel electrode was also used to study the efficiency of organic conducting thin films where the photovoltaic efficiency can be improved when the electrode separation distance is below the exciton diffusion length. Copper (II) phthalocyanine (CuPc) was thermally evaporated between the nano-gap electrodes formed by Au/Al₂O₃/Au tunnel junctions. A large photocurrent enhancement over 50 times that of bulk CuPc film was observed when the electrode gap distance approached 10 nm. CuPc diffusion length is seen to be 10 nm consistent with literature reports. All devices show diode I-V properties due to a large Schottky barrier contact resistance between the small top Au electrode and the CuPc film.

To add another dimension of nm-scale patterning, nanowires can be used as line-of-sight shadowmasks provided that nanowire location and diameter can be controlled. Lateral ZnO nanowires were selectively grown from the edge of a Si/Al₂O₃/Si multi-layer...
structure for potential integration into devices utilizing Si processing technology. Microstructural studies demonstrate a 2-step growth process in which the tip region, with a diameter ~ 10 nm, rapidly grew from the \( \text{Al}_2\text{O}_3 \) surface. Later a base growth with a diameter ~ 22 nm overgrew the existing narrow ZnO nanowire halting further tip growth. Kinetics studies showed surface diffusion on the alumina seed surface determined ZnO nanowire growth rate.

KEYWORDS: Molecular Devices, Tunnel Junctions, Photovoltaic Devices, Organic Semiconductor, Oxide Nanowires.
FABRICATION AND STUDY OF MOLECULAR DEVICES AND PHOTOVOLTAIC DEVICES BY METAL/DIELECTRIC/METAL STRUCTURES

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By

Bing Hu

Lexington, Kentucky

Director: Dr. Bruce J. Hinds, Professor of Materials Engineering

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2011

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This doctoral study is dedicated to my beloved family members:

My father Jiajiong Hu
My mother Chunyi Han
My wife Zhengchun Lu
& my daughter Sophia Yongxuan Hu
& Victoria Yongting Hu
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Chapter 1

Introduction

1.1 Development of Integrated Circuit (IC) industry

In electronics, an integrated circuit (also known as IC, microcircuit, silicon chip, or chip) is a chip of a semiconductor crystal in which many active or passive components have been miniaturized and integrated together to form a sophisticated circuit \(^{(1)}\). ICs are widely used in all electronic equipments today and have revolutionized the whole electronic world.

The IC industry has grown rapidly in the past half century. In 1958, Jack Kilby in Texas Instruments demonstrated the first working IC made of germanium. Half a year later, Robert Noyce in Fairchild Semiconductor made the first Silicon IC \(^{(2)}\). It was considered to be ridiculously optimistic to achieve a working IC consisting more than dozens of transistors at that time because the yield of each transistor was very low. With the technique development of thin film deposition, photolithography, etching, ion implant, impurity diffusion, and thermal oxidation, the IC industry has experienced four generations:

(1) Small-Scale Integration (SSI) having several transistors, early 1960s to middle 1960s.

(2) Medium-Scale Integration (MSI) having hundreds of transistors, in the late 1960s.
(3) Large-Scale Integration (LSI) having tens of thousands of transistors, in the middle 1970s.

(4) Very Large-Scale Integration (VLSI) having hundreds of thousands of transistors, and beyond, starting in 1980s and continuing through the present.

Since the last quarter of 2009, Intel began revenue production of i-series central processing units (CPUs) based on 32 nm logic technologies and the six-core i7 has over 1 billion transistors \(^{(3)}\). Intel is continuing to develop 28 nm technologies for static random access memories (SRAMs) and demonstrated working 22 nm SRAM chips. Recently, Intel proclaimed its new fab building plan at Arizona for 14 nm products. IBM, collaborating with AMD, Samsung, GLOBALFOUNDRIES, and Synopsys, also has developed their own 22 nm technique and is focusing on 14 nm technology development currently.

1.2 Limitation of Moore’s Law

Forty years ago, Intel co-founder Gordon Moore stated that the chip density would double every two years \(^{(4)}\), as well known as “Moore’s Law”. Gradually, people have accepted that the transistor’s density or clock speed doubles every 18 months. This predictive statement can be observed in Figure 1.1. With the current rate of technological advancement, Moore’s Law will be accurate for no more than 15 years before the minimum feature size reaches a molecular scale.
There are several limitations for conventional techniques to decrease the feature size beyond 10 nm. The first limitation is the wavelength of the light source. The general photolithography technique can only reach a critical dimension (CD) around 100 nm with a KrCl Excimer laser (157 nm). To reach a CD below 100 nm, E-beam lithography is generally used while its low throughput prevents the applications for mass production. Other options to reach the 10 nm scale include extreme UV lithography ($\lambda \approx 10\text{-}20$ nm) and X-ray lithography ($\lambda < 1$ nm). However, these techniques have difficulties of exposing radiation focusing, mask materials, and photoresists. Scientists and engineers have made great effort for the extreme UV lithography and SRAMs based on 22 nm technology has been achieved by Intel recently.

The second limitation is the thickness of the insulator layer in the field-effect transistor (FET) polysilicon-gate region. Several years ago, a 2 nm of thermally grown silicon oxide from the current channel was used to insulate the gate current. In order to keep Moore’s Law, the oxide layer has had to be attenuated continuously. However, this SiO$_2$ layer will not insulate effectively if the thickness is below 1.2 nm $^{(5)}$. High-k dielectric gate materials, normally HfO$_2$, have replaced SiO$_2$ as the insulating layer between the gate and current channel for Intel 45 nm processor technology. It is assumed that the HfO$_2$ thickness will approach the limit when the gate length is below 10 nm.

The third limitation is the electromigration of metal lines. This phenomenon will be more obvious when the dimension of metal lines gets smaller. Electromigration can break metal lines or crack the surrounding dielectric $^{(6)}$. Copper is now used instead of aluminum to reduce the electromigration phenomenon but it is not as easily processed as aluminum during fabrication. Considering further advancements in IC fabrication
techniques, the fact remains that the technologies and materials currently in use will reach their limits someday in future. Instead of the top-down route, the bottom-up route is another way for device fabrication. More and more scientists have started to focus on the fundamental components such as a single molecule or small groups of molecules to build up working electronic devices.

1.3 Development of molecular devices

Molecular devices can be divided into molecular rectifiers, molecular switches and molecular-scale wires, according to their applications. Carbon nanotubes (CNTs) are also considered as a kind of macro molecules and have become one of the hottest research areas among molecular devices.

1.3.1 Molecular rectifiers

The concept of a molecular device was introduced in 1974. A. Aviram and M.A. Ratner made a historical perspective that the molecule they studied would work as a molecular rectifier \(^{(7)}\). Figure 1.2a shows the molecular structure including an acceptor tetracyanoquinodimethane connected by a methylene bridge to a donor tetrathiofulvalene. Theatrical calculations showed that a rectification of current should be possible (Figure 1.2b). In 1997, R.M. Metzger et al. observed strong rectification behavior when studying Langmuir-Blodgett (LB) films of \(\gamma\)-(n-hexadecyl)quinolinium tricyanoquinodimethanide between metal electrodes \(^{(8)}\). In the same year, J. Joachim et al. described the first single-molecule electromechanical amplifier consisting of a single C\(_{60}\)
molecule between a scanning tunneling microscope (STM) tip and a conductive substrate. Their studies show excellent conductance through C60 because its molecular orbitals are shifted and broadened when the C60 is pressed by the STM tip. A gain of 5 is obtained by comparing the output voltage of 100 mV with the input voltage of 20 mV. (4-HOC6H4)3HC60, a derivative of C60, also shows rectification properties. A maximum rectification ratio of 47.5 was observed for this molecule.

### 1.3.2 Molecular switches

Molecular switches, the possible basic control units in future nano-devices, have been achieved using single molecules, carbon nanotubes, and nanoparticles. In 1998, S.T. Tans et al. fabricated an FET based on a carbon nanotube. A single carbon nanotube was connected by two Pt electrodes and the doped Si substrate acted as a back-gate. The experimental I-V curves indicate the current flow control by the gate voltage. Coulomb blockade was also observed based on the staircase I-V profiles. Recently, a light-driven molecular switch based on azobenzene molecules was reported. The trans conformation of azobenzene can be isomerized to the cis conformation with a beam of light with a wavelength of 365 nm and the reverse isomerization happens with a beam of light with a wavelength of 420 nm. The conductance difference between the trans and cis conformations enables the use of the azobenzene and possibly its derivatives as a single-molecule light-driven molecular switch with ON and OFF states. Applications of azobenzene include as photo-switchable molecular glue for DNA to control biological functions and the ionotropic glutamate receptor to control ion channels in cells. Many models have been built for molecular devices. For example, Y. Wada has proposed...
to use polythiophene chains or other molecular wires as the source, drain and gate. The calculated switching speed approaches 1 THz \(^{(12)}\). However, the challenge to make reproducible low-resistance contacts to the electrodes prevents their real production.

1.3.3 Molecular wires

Molecular-scale wires are also necessary for future molecular devices. Most researchers in this area are focusing on linear, conjugated oligomers \(^{(23-26)}\). Many potential molecules have been synthesized, such as metal-terminated carbon chains (molecule 1 in Figure 1.3) \(^{(27)}\), oligomeric linear prophyrin arrays (molecule 2 in Figure 1.3) \(^{(28)}\), and oligo(phenylene ethynylene)s (molecule 3 in Figure 1.3) \(^{(29, 30)}\). J.R. Reimers et al. \(^{(31)}\) studied over 100 such molecules as potential molecular wires (for example, molecule 4 in Figure 1.3) and concluded that \(\pi\) delocalization dominates the electronic properties of those systems. Higher delocalization supports longer distance communication between parts of molecules. In 1996, L.A. Bumm et al. succeeded in measuring the conductivity of one such molecule (molecule 5 in Figure 1.3) embedded in a self-assembled monolayer (SAM) of dodecanethiolate by STM \(^{(26)}\). STM images illustrated that this conjugated organic oligomers have a greater conductivity than dodecanethiolate.

1.3.4 Carbon nanotubes

The carbon nanotube is a very important platform for molecular devices and has many applications. Recently, carbon nanotubes have demonstrated promise for molecular scale wires due to their high conductance. The electrical properties of single-wall carbon
nanotubes (SWCNTs) are dependent on their specific chirality and diameter \(^{(32,33)}\). P.J. de Pablo \textit{et al.} characterized SWCNTs distributing between Au electrodes \(^{(34)}\). They found that the contact resistance between Au and CNTs is 44 kΩ and the tube resistivity is 0.15 Ω μm\(^{-1}\). These results indicate a great potential of CNTs as molecule-scale wires when the contact problem can be solved.

CNTs are also a good candidate for data storage. In 2000, C.M. Lieber \textit{et al.} proposed a nonvolatile random access memory (RAM) based on a suspended crossbar array of CNTs \(^{(35)}\). The status of the crossbar can be switched between suspended (ON) and contact (OFF) states. The ON state shows the domination of a van der Waals interaction between two crossed CNTs by applying voltage pulses of an opposite polarity. The ON state can be switched to the OFF state by applying a larger voltage pulse of an identical polarity. Experiment results show that the bias voltage for switching the crossbar ON is +/-5 V and that for switching OFF is 40 V. Information of ON or OFF of each crossbar can be read by measuring the resistance because the ON resistance is much lower than the OFF resistance. Such RAM devices were calculated to having a density of 10\(^{12}\) elements per cm\(^2\) and an operating frequency of 100 GHz.

The most important and promising application of CNTs is their use for mass transport. Our group successfully fabricated the well-ordered nanoporous membranes by incorporating an array of aligned CNTs across a polymer film \(^{(36)}\). Extremely high fluid velocities through the aligned CNT membrane were observed because of a frictionless surface at the carbon-nanotube wall \(^{(37)}\). For example, the observed water flow velocity is 43.9 cm s\(^{-1}\) at 1 bar, which is around 10\(^5\) times larger than the expected value of 5.7 × 10\(^{-4}\) cm s\(^{-1}\). Functionalization molecules were grafted at the entrance to CNTs’ cores and work
as a gatekeeper for a selective transportation of different molecules (ruthenium bipyridine [Ru-(bipy)$_3^{2+}$] and methyl viologen [MV$^{2+}$]) (38). These functionalized CNTs membranes have also been employed as the active element of a switchable transdermal nicotine delivery device able to switch between high (1.3 ± 0.65 μmol/hr·cm$^2$) and low (0.33 ± 0.22 μmol/hr·cm$^2$) fluxes, which coincides with therapeutic demand levels for nicotine cessation treatment (39).

With rapid development of molecular electronics, devices will become smaller, faster, and more efficient than conventional electronics. We should not be astonished when we hold molecular computers in our hands in several decades.

1.4 Electronic study of molecules

Studying electronic properties of molecules is the fundamental step to approach molecular devices. A variety of techniques, such as Langmuir-Blodgett (LB) film deposition (8, 40-42), scanning probe microscope (SPM) (9, 43, 44), hanging Hg drop electrode (45), metal wire crossing (46), and nanopores (47, 48) have been used to study the electronic transparency of molecules.

The first technique used to study electrical properties of molecules is the Langmuir-Blodgett (LB) method (49). A monolayer of organic materials was deposited between suitable substrates. C.M. Fisher et al. (41) used this technique to make Au/LB film/Au structures and measured the tunnel current through octasubstituted palladiumphthalocyanine (PcPd). J.R. Heath et al. (42) fabricated tunnel junctions with a structure of Al/Al$_2$O$_3$/Rotaxane LB film/Ti/Al and combined them together to obtain
AND and OR logic gates. The idea of hanging Hg drop electrode is similar as the normal LB route. An alkanethiol SAM forms on an Hg drop and builds up the tunnel structure of Hg/SAM/SAM/Hg\(^{(45)}\). Thereby, the electric conductance of alkanethiol molecules can be measured. The drawback of the LB film or SAM technique is an easy electrical short between electrodes. B.D. Boer \textit{et al.} \(^{(48)}\) developed a new design to support electrodes with patterned photoresist and molecules bridge electrodes \textit{via} pores throughout photoresist. The molecular junctions they made show excellent stability and reproducibility.

To study devices with fewer molecules, J.G. Kushmerick \textit{et al.} \(^{(46)}\) covered a Au wire with desired molecules and put another Au wire on it to form a cross-wire tunnel junction. The number of molecules between the crossed wires can be controlled to be around 1000. The distance between top and bottom wires was controlled by a Lorentz force generated by a DC current flowing through one wire in a magnetic field. C. Zhou \textit{et al.} \(^{(47)}\) used E-beam lithography and a following plasma etching to open a pore with a diameter of 30 nm in a suspended SiN membrane. Then, a Au film was deposited from the bottom side. No gold particles entered the nanopore because the Au crystallite size of 50 nm is larger than the pore diameter. Finally, a SAM layer of 4-thioacetylbiphenyl formed between Au electrodes through the nanopore.

Among all techniques mentioned in the first paragraph of this section, SPM is the most popular one for molecular study in the past decade. This technology includes scanning tunneling microscope (STM) and atomic force microscope (AFM). This technology uses cantilevers as one electrode with a tip area of 10 ~ 100 nm\(^2\). This decreases the probability of an electrical short dramatically. Another advantage of this method is its
ability to probe the electron current through a single molecule \(^{(9)}\). However, SPM is only a tool to study molecular electronic properties and can not to be integrated into molecular devices.

1.5 Single molecule devices

Fabricating single molecular devices is a goal for molecular device miniaturization. The main challenge is the precise control of a nano-gap between electrodes. Several techniques, including SPM \(^{(9, 43, 50)}\), mechanical break junction \(^{(51, 52)}\), electromigration break junction \(^{(53-58)}\), tip-end junction \(^{(59)}\) and shadow lithography \(^{(60)}\), have been developed to fabricate single-molecular-devices (SMD).

SPM is the most popular method to study molecular electrical properties. It is also the first technique to measure a single molecule \(^{[46]}\). The advantage of this SPM technique is getting electrical and morphological information of the studied single molecule simultaneously. STM study on C\(_{60}\) is a typical example \(^{(9)}\). The C\(_{60}\) resistance was about 54.8 MΩ corresponding to an electronic transparency of \(T = 2.3 \times 10^{-4}\). When an increasing compression was applied by the STM tip, the resistance of C\(_{60}\) decreased rapidly towards a quantum resistance limit of \(R_0 = h/2e^2\) (~12.9 kΩ). The molecular resistance measured by SPM is always larger than the real resistance. This is because a little gap between the tip and the molecule. W. Ho et al. used STM to build a metal-molecule-metal junction composed of two chainlike Au clusters and a single Cu(II) phthalocyanine (CuPc) molecule. The CuPc molecule was manipulated by the STM tip to bridge two Au clusters \(^{(50)}\). Although the molecular \(I/V\) properties of this tunnel junction
was not studied, this work shows a new insight to fabricate a single molecular device by the STM technique.

The principle of mechanical and electromigration break junction techniques are illustrated in Figure 1.4a & b, respectively. In either case, when a lithographically patterned narrow metal line is broken by a mechanical force or electromigration, molecules are introduced onto the two clean fracture surfaces to bridge the nano-gap. D.C Ralph et al. (53) used the later technique to study two related molecules containing a Co ion and observed the single-electron phenomena of Coulomb blockade and the Kondo effect. His group also realized a control of the electrode spacing via a combination of the mechanical and electromigration break junction techniques (52).

The shadow lithography technique is also used to study SMDs. Z. Bao et al. prepared tip-end junctions by depositing a Au layer on one side of a tip and evaporating another layer of Au on the other side of the same tip to form a nano-gap (59). T. Bjornholm et al. (60) used a suspended mask to cast two Au electrodes with a nano-gap. By using an oblique evaporation angle together with in situ conductance measurements, the tunneling gap between two electrodes can be well tuned to a few nanometers. The resistance of a few GΩ at 100K indicates a gap width of 2 nm. Then, molecules were introduced on the electrodes and single molecular transistors were observed.

Although single molecular transistors have been fabricated successfully by those techniques, the risk of electron tunneling through nano-scale metallic islands rather than the single molecule still exists. And, all of these techniques suffer from yield issues.
Therefore, fabricating a gap with a molecular scale without a risk of nano-scale metallic islands and a high yield is of interest in the SMD field.

1.6 Mechanism of electron transport through molecules

Metal/molecules/metal is the basic structure for molecular devices, as shown in Figure 1.5a. When the tunneling current is coherent in the bulk transport, this structure can be considered as a tunnel junction having a uniform barrier layer (Figure 1.5b). The current transport through individual molecules is different from bulk transport because of the inherently small size of molecules. The later part will be introduced in Section 1.6.4.

1.6.1 Bulk current transport through a molecular layer

1.6.1.1 Current tunneling through a potential barrier

To investigate tunneling, consider an electron incident from the top metal electrode to the bottom electrode in Figure 1.6. The barrier layer has a potential energy of $V$, which profile is given by

$$V = \begin{cases} 
V_0, & 0 \leq x \leq a, \\
0, & x < 0, \quad x > a,
\end{cases}$$

(1.1)

According to the classical physics, the electron will pass the potential barrier with a 100% certainty when the electron energy $E$ is larger than $V_0$ and the electron will be reflected from the barrier with a 100% certainty when $E$ is smaller than $V_0$. However, quantum mechanics show a more complicated behavior. Starting with Schrödinger’s equation,
\[
\left( -\frac{\hbar^2}{2m^*} \frac{d^2}{dx^2} + V(x) \right) \Psi(x) = E \Psi(x),
\]  
(1.2)

In region I \((x < 0)\) where \(V = 0\), equation (1.2) turns to

\[-\frac{\hbar^2}{2m^*} \frac{d^2}{dx^2} \Psi_1(x) = E \Psi_1(x),
\]  
(1.3)

which has solutions

\[
\Psi_1(x) = A e^{ik_1x} + B e^{-ik_1x},
\]  
(1.4)

where

\[
k_1^2 = \frac{2m^*E}{\hbar^2}.
\]  
(1.5)

In region II \((0 \leq x \leq a)\) where \(V = V_0\), equation (1.2) is

\[
\left( -\frac{\hbar^2}{2m^*} \frac{d^2}{dx^2} + V(x) \right) \Psi_2(x) = E \Psi_2(x),
\]  
(1.6)

which has solutions

\[
\Psi_2(x) = C e^{ik_2x} + D e^{-ik_2x},
\]  
(1.7)

where

\[
k_2^2 = \frac{2m^*(E-V_0)}{\hbar^2}.
\]  
(1.8)

In region III \((x > a)\), equation (1.2) is

\[-\frac{\hbar^2}{2m^*} \frac{d^2}{dx^2} \Psi_3(x) = E \Psi_3(x),
\]  
(1.9)

which has solutions
\[ \Psi_3(x) = F e^{i k_3 x} + G e^{-i k_3 x}, \]  
(1.10)

where

\[ k_3^2 = \frac{2m^*E}{\hbar^2} = k_1^2. \]  
(1.11)

There is no reflection when electrons enter region III, so \( G = 0 \) and we have

\[
\begin{aligned}
\Psi_1(x) &= A e^{i k_1 x} + B e^{-i k_1 x} \\
\Psi_2(x) &= C e^{i k_2 x} + D e^{-i k_2 x} \\
\Psi_3(x) &= F e^{i k_1 x}
\end{aligned}
\]  
(1.12)

Considering the boundary conditions, \( \Psi_1 = \Psi_2 \) at \( x = 0 \) and \( \Psi_2 = \Psi_3 \) at \( x = a \), we have

\[
\frac{F}{A} = \frac{4k_1 k_2 e^{i(k_2-k_1)a}}{(k_1+k_2)^2-(k_1-k_2)^2 e^{2iak_2}}
\]  
(1.13)

So a tunneling probability is defined as

\[
T = \left| \frac{F}{A} \right|^2 = \frac{4E(E-V_0)}{V_0^2 \sin^2(k_2a) + 4E(E-V_0)}
\]  
(1.14)

and a reflection probability is defined as

\[
R = \left| \frac{B}{A} \right|^2 = \frac{V_0^2 \sin^2(k_2a)}{V_0^2 \sin^2(k_2a) + 4E(E-V_0)}.
\]  
(1.15)

(1.14) can be rewritten as

\[
T = \left( 1 + \frac{V_0^2 \sin^2(k_2a)}{4E(E-V_0)} \right)^{-1}
\]  
(1.16)

When \( E > V_0 \), it can be seen that a full transmission occurs when \( \sin(k_2a) = 0 \), that is, when
\[ k_2 = n\pi / a, \quad n = 0, 1, 2, 3, .... \] (1.17)

An important case is when \( E < V_0 \). This is the general condition for most electronic devices and also the case for our experiments. Therefore,

\[
\sin \left( \sqrt{\frac{2m_e^* (E - V_0)}{\hbar^2}} a \right) = \sin \left( i \sqrt{\frac{2m_e^* (V_0 - E)}{\hbar^2}} a \right) = i \sinh \left( \sqrt{\frac{2m_e^* (V_0 - E)}{\hbar^2}} a \right)
\]

\[
\rightarrow i \frac{\sqrt{2m_e^* (V_0 - E)}}{\hbar} a \quad \approx \quad \frac{i}{2} e^{\alpha a}
\] (1.18)

where \( \alpha = \sqrt{\frac{2m_e^* (V_0 - E)}{\hbar^2}} > 0 \),

(1.19)

so that \( T \rightarrow \frac{16E(V_0 - E)}{V_0^2} e^{-2\alpha a} \).

(1.20)

It is clear that the tunneling probability \( T \) is exponentially decaying as a function of the barrier width \( a \). And this explains why the tunneling can become a significant problem when the gate oxide layer is very thin for metal-oxide-semiconductor field effect transistors (MOSFETs).

### 1.6.1.2 Molecular conductance by coherent tunneling

The current passing through molecules is affected by many factors. These factors can be divided into two groups. The intrinsic factors include molecular length, conformation, and highest occupied molecular orbital-lowest unoccupied molecular orbital (HOMO-LUMO) gap. The extrinsic factors include the electrode work function and the contact between molecules and electrodes.
Considering the coherent tunneling current, conductance $G$ of the metal/molecule/metal junction can be described by the Landauer formula $^{(61)}$:

$$G = \frac{2e^2}{h} T$$  \hspace{1cm} (1.21)

where $T$ is the tunneling probability introduced in Section 1.6.1.1 and can be divided into three components:

$$T = T_{tc} \cdot T_{bc} \cdot T_{mol}$$  \hspace{1cm} (1.22)

where $T_{tc}$ and $T_{bc}$ gives the efficiency of electron transport across the top and bottom contacts in Figure 1.5a. $T_{mol}$ gives the efficiency of electron transport across the molecule which can be considered as a rectangular barrier introduced in Section 1.6.1.1. Here, $T_{mol}$ is simplified from (1.19) and given by

$$T_{mol} = e^{(-\beta l)}$$  \hspace{1cm} (1.23)

where $l$ is the length of the molecule, similar as the potential barrier width $a$ in Figure 1.6. In equation (1.18), $(V_0 - E)$ is the energy gap between the particle or electron in Figure 1.6. When no bias is applied on molecules, the energy gap is $\phi$, where $\phi$ is the barrier height for tunneling through LUMO ($\phi = (E_F - E_{LUMO})$) or through HOMO ($\phi = (E_{HOMO} - E_F)$), $E_F$ is the Fermi level of the electrode. Figure 1.7a shows the schematic energy diagram and $\phi$ is set as $(E_{HOMO} - E_F)$. When a bias $V$ is applied on molecules, the average energy gap will turn to $(\phi - (eV/2))$, as shown in Figure 1.7b. Therefore, the tunneling decay parameter $\beta$ is derived from (1.19) and given by:

$$\beta = 2 \sqrt{\frac{2m_e^* (\phi - (eV/2))}{\hbar^2}}$$  \hspace{1cm} (1.24)
B. Boer et al. summarized the study of molecular conductance and plotted the single alkane-based molecular resistance with the number of carbon atoms present in the alkane chain (62). Three large clusters of data were found to be compiled from different measurement methods. The low contact resistance group consists of STM and CP-AFM measurements, with alkanedithiol molecules chemically bonded to both electrodes, having small $T_{tc}$ and $T_{bc}$. The medium contact resistance group consists of measurements on larger device areas with only one end of the molecule chemisorbed at the electrode. And, the large contact resistance group is composed of molecules without any chemistry adsorption on electrodes. All three groups show a similar exponential increase of resistance when increasing alkane chain length. The $\beta$ has a value of $0.7 \sim 1.1 \text{Å}^{-1}$.

Figure 1.8 (63) shows possible paths for current transport through molecular junctions. They are through-bond tunneling (I), through-space tunneling (II) and a combination of both (III). Lots of experiments prove that the dominant current transport is through-bond tunneling, in which the electrons follows the bond overlaps along the molecules (64). It’s well known that the current through conjugated molecules is much higher than that through saturated molecules with a similar length. The current difference is generally on the order of 1-1.5 (65). The main reason is the smaller $\phi$ of the $\pi$-bond of conjugated molecules (about 3 eV) compared with $\phi$ of the $\sigma$-bond of saturated ones (about 8 eV). This results in a tunneling decay parameter $\beta$ of 0.2-0.6 $\text{Å}^{-1}$ for $\pi$-bond molecules and 0.6-1.0 $\text{Å}^{-1}$ for $\sigma$-bond molecules, according to formula (1.24) (63).

1.6.1.3 Simmons model
The tunneling decay parameter $\beta$ is used to describe the transmittance property of a molecule. This part has been introduced in last section. To describe the insulating property of a dielectric layer, a barrier thickness (Å or nm) and a barrier height (eV) are generally used, especially for tunnel junctions. There are many simulation models and Simmons model \(^{(66)}\) is the most popular one used for tunnel junctions.

The electron can pass through a tunnel junction in two ways: (1) The electron has enough thermal energy to overcome the potential barrier and flow in the conduction band; (2) The barrier is thin enough for the electron to penetrate by an electric tunnel effect. In this section, only the tunneling effect is considered.

Assuming an electron can penetrate a potential barrier of height $V(x)$ in the x direction, as shown in Figure 1.9, its penetration probability $D(E_x)$ is given by the Wentzel–Kramers–Brillouin (WBK) approximation \(^{(67)}\):

$$D(E_x) = \exp \left\{ -\frac{4\pi}{\hbar} \int_{-s}^{s} [2m(V(x) - E_x)]^{\frac{1}{2}} dx \right\}$$

\( (1.25) \)

where $E_x = \frac{mv_x^2}{2}$, and is the incident electron energy in the x direction. Therefore, the number $N_1$ of the electrons tunneling through this barrier from left electrode to right electrode is given by

$$N_1 = \int_0^{v_m} v_x n(v_x) D(E_x)dv_x = \frac{1}{m} \int_0^{E_m} n(v_x) D(E_x) dE_x$$

\( (1.26) \)
where $E_m$ is the maximum energy of electrons in the electrode, and the $n(v_x)dv_x$ is the electron number per unit with a velocity from $v_x$ to $v_x+dv_x$. The velocity distribution of electrons in the electrodes is considered to be isotropic. The electron number per unit with a velocity between a usual infinitesimal limits is given by

$$n(v)dv_x dv_y dv_z = \left( \frac{2m^4}{h^3} \right) f(E)dv_x dv_y dv_z$$  \hspace{1cm} (1.27)

where $f(E)$ is the Fermi-Dirac distribution function. Therefore, from Equation (1.27)

$$n(v_x) = \frac{2m^4}{h^3} \int_{-\infty}^{\infty} f(E)dv_y dv_z = \frac{4\pi m^2}{h^3} \int_0^{\infty} f(E)dE_r$$  \hspace{1cm} (1.28)

where $v_r^2 = v_y^2 + v_z^2$, $E_r = mv_r^2/2$. Substituting Equation (1.28) in Equation (1.26) yields

$$N_1 = \frac{4\pi m^2}{h^3} \int_0^{E_m} D(E_x) dE_x \int_0^{\infty} f(E)dE_r$$  \hspace{1cm} (1.29)

In a similar manner, if a positive potential $V$ is applied on the right electrode in Figure 1.9, the tunnel probability $D(E_x)$ from the right electrode to the left electrode is given

$$N_2 = \frac{4\pi m^2}{h^3} \int_0^{E_m} D(E_x) dE_x \int_0^{\infty} f(E + eV)dE_r$$  \hspace{1cm} (1.30)

Therefore, the total flow of electrons $N$ through the barrier is

$$N = N_1 - N_2 = \frac{4\pi m^2}{h^3} \left\{ \int_0^{\infty} [f(E) - f(E + eV)]dE_r \right\} \times \int_0^{E_m} D(E_x) dE_x$$  \hspace{1cm} (1.31)
We define

\[ \gamma = \frac{4\pi m^2}{h^3} \int_0^\infty [f(E) - f(E + eV)]dE \]

(1.32)

Therefore, we have

\[ J = \int_0^{E_m} D(E_x) \gamma dE_x \]

(1.33)

In Figure 1.9, \( V_x = \eta + \varphi(x) \), Equation (1.25) becomes

\[ D(E_x) = \exp \left\{ -\frac{4\pi}{h} \left(2m\right)^{1/2} \int_{s_1}^{s_2} [\eta + \varphi(x) - E_x]^{1/2} dx \right\} \approx \exp \left[ -A(\eta + \bar{\varphi} - E_x)^{1/2} \right] \]

(1.34)

where \( \bar{\varphi} \) is the mean barrier height above Fermi level of the negatively biased electrode and defined by \( \bar{\varphi} = \frac{1}{\Delta s} \int_{s_1}^{s_2} \varphi(x) \, dx \), and \( A = (4\pi\Delta s/h) (2m)^{1/2} \). Here, \( \beta \) is generally close to 1. When the temperature is 0K, we have

\[ \gamma = \left\{ \begin{array}{ll}
\left(\frac{4\pi m e}{h^3}\right)(eV), & 0 < E_x < \eta - eV \\
\left(\frac{4\pi m e}{h^3}\right)(\eta - E_x), & \eta - eV < E_x < \eta \\
0, & E_x > \eta
\end{array} \right. \]

(1.35)

Substituting Equations (1.34) & (1.35) in Equation (1.33) yields
\[ J = \frac{4\pi me}{\hbar^3} \left\{ eV \int_0^{\eta-eV} \exp \left[ -A(\eta + \bar{\phi} - E_x)^\frac{1}{2} \right] dE_x - \bar{\phi} \int_{\eta-eV}^\eta \exp \left[ -A(\eta + \bar{\phi} - E_x)^\frac{1}{2} \right] dE_x \right\} \]

The first part of the integrals yields

\[ \left( \frac{8\pi meV}{\hbar^3 A^2} \right) \left\{ \left[ A(\bar{\phi} + eV)^\frac{1}{2} + 1 \right] \exp \left[ -A(\bar{\phi} + eV)^\frac{1}{2} \right] - \left[ A(\bar{\phi} + \eta)^\frac{1}{2} + 1 \right] \exp \left[ -A(\bar{\phi} + \eta)^\frac{1}{2} \right] \right\} \]

(1.37)

Because the second term \(<\text{ first term and } A(\bar{\phi} + eV)^\frac{1}{2} >> 1\), Equation (1.37) turns into

\[ \left( \frac{8\pi me^2}{\hbar^3 A} \right) V (\bar{\phi} + eV)^\frac{1}{2} \exp \left[ -A(\bar{\phi} + \eta)^\frac{1}{2} \right] \]

(1.38)

The second part of the integrals has a similar form as the first part. Therefore,

\[ \left( \frac{8\pi me}{\hbar^3 A^2} \right) \bar{\phi} \left\{ \left[ A\bar{\phi}^2 + 1 \right] \exp \left( -A\bar{\phi}^2 \right) - \left[ A(\bar{\phi} + eV)^\frac{1}{2} + 1 \right] \exp \left[ -A(\bar{\phi} + eV)^\frac{1}{2} \right] \right\} \]

(1.39)

The third part of the integrals has the form

\[ \int z^2 e^{-Az} \, dz = -e^{-Az} \left( \frac{z^3}{A} + \frac{3z^2}{A^2} + \frac{6z}{A^3} + \frac{6}{A^4} \right) \]

(1.40)

where \( z^2 = \eta + \bar{\phi} - E_x \). The third and fourth terms in the parentheses are negligible comparing with the first two terms. Therefore, Equation (1.40) turns into
Substituting Equations (1.38), (1.39), and (1.41) in Equation (1.36) yields

\[
J = j_0 \left\{ \phi \exp \left( -A \phi^\frac{1}{2} \right) - (\phi + eV) \exp \left[ -A(\phi + eV)^{\frac{1}{2}} \right] \right\} \tag{1.42}
\]

where \(J_0 = e/2\pi h(\beta \Delta s)^2\).

Generally, the tunnel junctions are considered as a rectangular potential barrier, as shown in Figure 1.7a. In this dissertation, the dielectric layer between electrodes is aluminum oxide. The barrier height of aluminum oxide is typically ranging from 1 eV to 3 eV \(^{(68)}\).

The typical applied voltage \(V\) is from 0.1 V to 0.5 V, smaller than \(\phi/e\). Figure 1.7b shows the schematic energy diagram in this intermediate-voltage range: \(V < \phi/e\). Therefore, \(\Delta s = s\) and \(\phi = (\phi - eV/2)\). Substituting these values to Equation (1.42), the observed current density \(J\) is described as

\[
J = \frac{e}{2\pi h(\beta s)^2} \left\{ \left( \phi - \frac{eV}{2} \right) \exp \left[ -\frac{4\pi \beta s}{h} \left( \frac{1}{2m} \right) \left( \phi - \frac{eV}{2} \right)^{\frac{1}{2}} \right] \right\} - \left( \phi + \frac{eV}{2} \right) \exp \left[ -\frac{4\pi \beta s}{h} \left( \frac{1}{2m} \right) \left( \phi + \frac{eV}{2} \right)^{\frac{1}{2}} \right] \}
\]
where \( e \) is electron charge, \( h \) is Planck’s constant, \( \phi \) is the barrier height, \( s \) is the barrier thickness, \( V \) is the applied bias and \( \beta \) is a parameter determined by the tunnel junction properties and the applied bias \( V \). Here, \( \beta \) equals to 1. Simmons fitting is used to figure the insulating properties of most devices in this dissertation.

### 1.6.1.4 Coulomb blockade

The most popular structure of molecular devices is metal/molecules/metal. When the size of electrodes shrinks to a nanoscale, Coulomb blockade will become a fundamental effect. To simply this problem, consider two electrodes separated by an insulator layer first. The charge and voltage are proportional following

\[
Q = C \cdot V,
\]

where \( Q \) is the charge on the electrodes, \( C \) is the capacitance, and \( V \) is the voltage between two electrodes. The electrostatic energy stored in this capacitor is

\[
E = C \cdot V^2 = \frac{Q^2}{2 \cdot C}.
\]

The simplest capacitor is formed by two parallel plates of a area \( A \) and a distance \( d \). For this configuration,

\[
C = \varepsilon \cdot \frac{A}{d},
\]

where \( \varepsilon \) is the permittivity of the material between two plates. Table 1.1 shows the capacitance values and energy change due to the transfer of a single electron through a nano- or micro-capacitor. Here, a vacuum is assumed between two electrodes \( (\varepsilon = \varepsilon_0) \).
When the tunneling area is 10 μm × 10 μm, the change in energy due to the transfer of a single electron (ΔE) is only $1.8 \times 10^{-7}$ eV and is negligible. Coulomb blockade becomes obvious when the tunneling area decreases to 5 nm × 5 nm. 0.73 V is needed to apply on electrodes for a single electron to transport, as shown in Figure 1.10. J. Park et al. put [Co(tpy-(CH$_2$)$_5$-SH)$_2$]$^{2+}$ molecules between nanoscale Au electrodes and the $I$-$V$ curves show the coulomb blockade phenomenon at the room temperature ($^{53}$).

Temperature plays an important role in Coulomb blockade effect. Thermal energy is available when $T > 0$ K. To keep $\Delta E$ much larger than the thermal energy,

$$\frac{q^2}{2\mathcal{C}} \gg \frac{1}{2} k_B T,$$

or

$$\mathcal{C} \ll \frac{q^2}{k_B T},$$

is needed to be satisfied to observe the Coulomb blockade, where $k_B$ is Blotzmann’s constant. For the nanocapacitor in Table 1.1, $T \ll 1.7 \times 10^5$ K, is the lab condition. However, for the microcapacitor in Table 1.1, $T \ll 4.3 \times 10^{-3}$ K, is very difficult to achieve.

1.6.2 Current transport through a single molecule

1.6.2.1 Double barrier tunneling
A single molecule bridging two electrodes acts as a quantum dot. This metal/single molecule/metal system can be simulated as a double barrier tunnel junction, as shown in Figure 1.11a&b. The analysis of the double barrier tunnel junction is same as procedures at Section 1.6.1.1. The only difference is that five regions should be considered and four interfaces match boundary conditions. The result for the transmission coefficient of the double barrier system in Figure 1.11b is

\[
T = \left(1 + \frac{4R_1}{T_1^2} \sin^2(k_1 L - \theta)\right)^{-1},
\]

where \( R_1 \) and \( T_1 \) are the transmission and reflection coefficient for a single barrier of a width \( a \), given by (1.15) and (1.14), respectively. \( L \) is the length of the well between barriers, and

\[
\tan \theta = \frac{2k_1 k_2 \cos(k_2 a)}{(k_1^2 + k_2^2) \sin(k_2 a)},
\]

where

\[
k_1^2 = \frac{2m^* E}{\hbar^2}, \quad k_2^2 = \frac{2m^* (E-V_o)}{\hbar^2}.
\]

From (1.30), \( T \) will become unity when

\[
\sin(k_1 L - \theta) = 0 \quad \Rightarrow \quad k_1 L - \theta = n\pi, \quad n = 0, 1, 2, \ldots
\]

For a simple case, assume that \( V_0 \gg E \), so \( |k_2| \gg |k_1| \Rightarrow \tan \theta \to 0 \Rightarrow \theta \to 0 \), leading to \( k_1 L = n\pi \). Putting this result into (1.51), we have

\[
E = E_n = \frac{\hbar^2}{2m^* L} \left(\frac{n\pi}{L}\right)^2,
\]

which is exactly same as the result for quantized energy levels in a one-dimensional
quantum well \(^{69}\). Equation (1.53) reveals that transmission of the particle in Figure 1.10b reaches maximum when \(E = E_n\), which is defined as the quasi-bound state of the well in the double barrier system.

### 1.6.2.2 Coulomb blockade in a double junction system

Coulomb blockade also happens for the double barrier tunnel junction with a sufficiently low temperature or a small capacitance described in Section 1.6.1.4. Figure 1.12 shows the equivalent circuit of a metal/single molecule/metal structure. For each tunnel junction, we have

\[
Q_a = C_a V_a, \quad Q_b = C_b V_b. \tag{1.54}
\]

So the energy stored in the capacitors is

\[
E_s = \frac{Q_a^2}{2c_a} + \frac{Q_b^2}{2c_b} = \frac{1}{2} (C_a V_a^2 + C_b V_b^2). \tag{1.55}
\]

For the circuit, we have

\[
\begin{align*}
Q &= Q_b - Q_a = nq_e \\
V_s &= V_a + V_b \\
C_s &= C_a + C_b
\end{align*} \quad \Rightarrow \quad \begin{align*}
V_a &= \frac{1}{c_s} (V_s C_b - nq_e) \\
V_b &= \frac{1}{c_s} (V_s C_a + nq_e). \tag{1.56}
\end{align*}
\]

Therefore, equation (1.55) can be written as

\[
E_s = \frac{1}{2c_s} (C_a C_b V_s^2 + (nq_e)^2). \tag{1.57}
\]
Assume that there are \( n \) electrons on the single molecule and let one electron tunnel onto the molecule through junction \( b \). From equation (1.56), the voltage change in junction \( a \) and \( b \) is

\[
\Delta V_a = \Delta V_b = \frac{q_e}{c_s}.
\]  

(1.58)

At the same time, the charge change in junction \( a \) is

\[
\Delta Q_a = C_a \Delta V_a = \frac{C_a q_e}{c_s},
\]  

(1.59)

and the associated work done by the power supply is

\[
W = \Delta Q_a V_s = \frac{C_a q_e}{c_s} V_s.
\]  

(1.60)

So, the total energy change when the electron is tunneling through junction \( b \) is

\[
\Delta E = \Delta E_s - W
\]

\[
= \frac{1}{2c_s} \left( C_a C_b V_s^2 + (nq_e)^2 \right) - \frac{1}{2c_s} \left( C_a C_b V_s^2 + ((n+1)q_e)^2 \right) - \frac{C_a q_e}{c_s} V_s.
\]  

(1.61)

The energy change should be positive (\( \Delta E > 0 \)) and we have

\[
V_s > \frac{-q_e}{c_a} \left( n + \frac{1}{2} \right).
\]  

(1.62)

Using the same procedures to deal with the electron tunneling off the molecule through junction \( a \), we have

\[
V_s > \frac{q_e}{c_b} \left( n - \frac{1}{2} \right).
\]  

(1.63)
For a symmetrical molecule, \( C_a = C_b = C \). And if \( n = 0 \), we would get

\[
|V_s| > \frac{|q_e|}{2C} \Rightarrow E_c = \frac{q_e^2}{2C}.
\]

(1.64)

same as the Coulomb blockade for the single capacitor in (1.45).

Now considering one electron already tunneling onto the molecule through junction \( b \), a second electron tunnels onto the molecule through junction \( b \), the energy change should be

\[
\Delta E = \frac{1}{2C_s} \left( C_a C_b V_s^2 + \left( (n + 1)q_e \right)^2 \right) - \frac{1}{2C_s} \left( C_a C_b V_s^2 + \left( (n + 2)q_e \right)^2 \right) - \frac{C_a q_e}{C_s} V_s,
\]

(1.65)

and enforcing \( \Delta E > 0 \) with special conditions \( (C_a = C_b = C \) and \( n = 0 \)) leads to

\[
|V_s| > \frac{3|q_e|}{2C}.
\]

(1.66)

In general, we have

\[
|V_s| > \frac{(2m-1)|q_e|}{2C},
\]

(1.67)

where \( m = 1, 2, 3, \ldots \), for 1, 2, 3, ... electron tunneling events, respectively. Therefore, if electrons are tunneling through the single molecule one by one in Figure 1.12a, the \( I-V \) curve will show discrete voltage steps called a Coulomb staircase, as shown in Figure 1.13. R.C. Jaklevic et al. \(^{70}\) used the STM technique to observe this phenomenon for an In droplet at 4.2 K, which worked as a quantum dot. R. Negishi et al. \(^{71}\) put a Au nanoparticle between an electrode gap with a 10 nm scale and observed the Coulomb steps at 10 K. Y. Wakayama et al. \(^{72, 73}\) deposited a porphyrin derivative molecule between SiO\(_2\) layers to form a double-barrier tunneling junction, consisting of a

1.6.2.3 Electron transport through a single molecular transistor

The properties of a metal/single molecule/metal structure can be better controlled when a gate terminal covered with an insulating layer is added below the single molecule, as shown in Figure 1.14. This device is called a single molecular transistor. The gate voltage $V_g$ is used to control the HOMO or LUMO level of this molecule. Therefore, the source-drain voltage $V_s$ required to drive a current through the transistor can be controlled by $V_g$.

Following all procedures in the previous section, we have

$$
\begin{align*}
Q_a &= C_a V_a, \quad Q_b = C_b V_b, \quad Q_g = C_g (V_g - V_b), \\
Q &= Q_b - Q_a - Q_g = n q_e, \\
V_s &= V_a + V_b, \quad V_g = V_{gg} + V_b,
\end{align*}
$$

and can derive the energy stored in the capacitors is

$$
E_s = \frac{Q_a^2}{2C_a} + \frac{Q_b^2}{2C_b} + \frac{Q_g^2}{2C_g} = \frac{1}{2 C_s} \left( C_g C_a (V_s - V_g)^2 + C_a C_b V_s^2 + C_b C_g V_g^2 + Q^2 \right),
$$

where $C_s = C_a + C_b + C_g$.

Assume that an electron tunnels through junction $b$ onto the HOMO or LUMO level of this molecule, the change of the total energy should be

$$
\Delta E = \Delta E_s - (W_a + W_g) > 0
$$

$$
\Rightarrow \frac{1}{2 C_s} (n q_e)^2 - \frac{1}{2 C_s} ((n + 1) q_e)^2 - \frac{C_a q_e}{C_s} V_s - \frac{C_g q_e}{C_s} V_g > 0
$$
\[ q_e \left( n + \frac{1}{2} \right) + C_a V_s + C_g V_g > 0. \]  
(1.70)

In a same way, when an electron on the HOMO or LUMO level of this molecule tunnels off the molecule through junction \( a \), we can get

\[ q_e \left( -n + \frac{1}{2} \right) + V_s \left( C_b + C_g \right) - C_g V_g > 0. \]  
(1.71)

At the initiation of current flow, there is no charge on the molecule \((n=0)\). Therefore, the first electron tunnels into the molecule through junction \( b \) and we have

\[ V_s > \frac{1}{C_a} \left( -\frac{q_e}{2} - C_g V_g \right) \]  
(1.72)

derived from equation (1.70). Now \( n = 1 \) and the electron tunnels off the molecule through junction \( a \). We can get

\[ V_s > \frac{1}{C_b + C_g} \left( \frac{q_e}{2} + C_g V_g \right) \]  
(1.73)

derived from equation (1.71).

Now there is an electron on the molecule. If a second electron want to tunnels through junction \( b \) onto the molecule and tunnels through junction \( a \) off the molecule, we can get

\[
\begin{align*}
V_s &> \frac{1}{C_a} \left( -\frac{3q_e}{2} - C_g V_g \right) \\
V_s &> \frac{1}{C_b + C_g} \left( \frac{3q_e}{2} + C_g V_g \right)
\end{align*}
\]  
(1.74)

similar as the equation (1.66) introduced in Section 1.6.2.2. Continuing in this manner and considering the opposing tunneling conditions, we can obtain the Coulomb diamonds shown in Figure 1.15. These special diamond patterns are the proof for single molecular transistors \((53-55, 60, 74)\).
1.7 Organic semiconductor

An organic semiconductor is an organic material showing semiconductor properties. Organic semiconductors are composed of conjugated molecules, oligomers and polymers where electrons or holes can transport via $\pi$-electron overlapping with hopping and tunneling processes. Organic semiconductors have become an attractive research area with their potential application in organic solar cells with very large area production techniques similar to what has produced ‘Saran wrap’.

1.7.1 Organic solar cells

Organic solar cells (OSCs) have attracted a great deal of attention because of their low production cost, inexpensive substrates and robust mechanical flexibility. However, the power conversion efficiency of OSCs are very low (normally 3~5%) and hinders their widespread applications. The power conversion process in OSCs has three main steps: exciton generation by optical absorption, exciton dissociation into carriers, and carrier collection at the electrodes. Because organic semiconductors have highly localized states, generally, only a small fraction of the excitons generated by light near the donor-acceptor interface contribute to the final photocurrent because the thickness of organic polymers between electrodes is far larger than the exciton diffusion lengths (close to or below 10 nm) of these materials. Most electrons recombine with holes rather than reaching the donor-acceptor interface or electrodes. It is hypothesized that OSCs’ photovoltaic efficiency can be much improved when the carrier travel distance is controlled below 10 nm scale. However, it is challenging to fabricate large area ultrathin cells (organic layer thickness less than 10 nm) between two thick electrodes without
electrical shorts. Ultra-high-voltage organic molecular beam evaporation (UHV-MBE) has been used to build a donor-acceptor multiple heterojunction device (each layer thinner than 10 nm). This device showed a high external quantum efficiency of ~ 75% under an applied field. A more common way to reduce the travel distance of electron-hole pairs is by blending donor and acceptor layers. Using this technique, the quantum efficiency of bulk heterojunctions has been greatly improved. And power conversion efficiencies over 5% for metal phthalocyanine (MePc) based OSCs and 7% for thieno[3,4-b]thiophene and benzodithiophene polymers (PTBs) based OSCs have been realized. The interdigitated morphology of bulk heterojunctions is composed of well-organized nano-structures considered to be the ideal structure for OSCs. However, these structures are difficult to fabricate over large areas because of poor controllability of polymers.

In this dissertation, we deposited the organic semiconductor between nano-gap electrodes at the exposed edge of a metal/dielectric/metal structure. The carrier travel distance can be controlled below 10 nm and a great photovoltaic enhancement was detected.

1.7.2 Organic materials in organic solar cells

Organic materials in OSCs are divided into two groups: hole-conducting materials (p-type) working as the electron donor and electron-conducting materials (n-type) working as the electron acceptor. A donor layer and an acceptor layer are generally deposited together between electrodes to get a high dissociation efficiency for electron-hole pairs in the sun light. Metal Phthalocyanine (MePc), poly(p-phenylenevinylene) (PPV) and its
derivatives, and poly(3-hexylthiophene-2,5-diyi) (P3HT) are the popular electron donors; Perylene, buckminster fullerene C\textsubscript{60} and its derivatives are the popular electron accepters (Figure 1.16).

At the beginning of solar cell development, MePc and Perylene were often incorporated into evaporated solar cells because of their stability and facile deposition by thermal evaporation \(\textsuperscript{(88, 89)}\). The low charge carrier mobility in these materials makes them be regarded as insulators. To increase the charge carrier concentration, MePc was exposed to oxygen or strong oxidizing agents such as iodine \(\textsuperscript{(89, 90)}\) while Perylene was exposed to hydrogen \(\textsuperscript{(90)}\). The final doped MePc/Perylene bilayer devices can work as classical \(p-n\) junctions \(\textsuperscript{(91-93)}\). In this dissertation, Copper Phthalocyanine (CuPc) was used as the organic material for the photocurrent study in Chapter 5.

In 1992, the photo-induced charge transfer from a conjugated polymer to a C\textsubscript{60} layer was first reported by Sariciftci \textit{et al} \(\textsuperscript{(94)}\). Since then, the polymer-fullerene devices become the most popular solar cells for research. In 1995, Yu et al. used a blend of 2-methoxy-5-(2-ethylhexyloxy)-polyphenylenevinylene (MEH-PPV) and [6,6]-phenyl C\textsubscript{61} butyric acid methyl ester (PCBM, a kind of C\textsubscript{60} derivative) to build the bulk heterojunction (BHJ) and got a power efficiency of \(~ 1\%\). This is a major breakthrough for OSCs \(\textsuperscript{(83)}\). Today, organic photovoltaics are presented by BHJ OSCs based on P3HT and PCBM materials. The efficiency of these BHJ OSCs ranges from 4-5\% \(\textsuperscript{(95-99)}\). However, this P3HT:PCBM system is already approaching optimal device performance considering the poor material mobility properties. To improve OSCs efficiency further towards 10\%, new materials and nm-scale electrode geometries are needed. For instance an array of nanoscale
interpenetrating bicontinuous network of p-n materials can have the appropriate electrodes within the exciton diffusion length.

1.8 The novel design of a metal/insulator/metal structure towards molecular devices

Considering the precise control of film thickness with angstrom-level by film deposition, our group has developed a novel and simple method to fabricate nano-gap electrodes with the critical dimension based on easily controlled insulator film thickness (100). As shown in Figure 1.17, a metal wire (5 μm wide, 10 nm thickness) as the bottom electrode was deposited first and another wire (5 μm wide, alumina 2nm/metal 10 nm) as the top electrode was deposited across the bottom electrode by a lift-off process. Then, molecules were introduced to bridge the top and bottom electrodes at the exposed edge of metal/dielectric/metal structure. For Ni/Al₂O₃/Au samples, the current increased after molecules attachment and returned to the background level after disconnecting molecules to the Au electrode by thiol-exchange reaction. The same reversible behavior was observed after the cycle was repeated. This control experiment illustrates that the increased current passes through molecules bridging two electrodes and do not originated from the random breakdown of electrodes. Simmons fitting analysis shows the molecular barrier thickness of ~ 1 nm and the molecular barrier height of ~ 0.7 eV, respectively.

The most obvious advantage for our fabrication method is the precise control of gap distance between two electrodes. The gap between electrodes is controlled by the dielectric film thickness. This can be controlled in an angstrom scale by a normal deposition process. This fabrication process is more stable and convenient than all
techniques mentioned in chapter 1.5. Our molecular devices are also a type of reversible sensing devices. Molecules locating on the exposed metal surface are easily modified or exchanged.

1.9 Challenges

The nano-gap formed at the exposed edge of a metal/dielectric/metal structure is a good platform to study molecular conduction. The lift-off method is simple and has a low cost. But the repeatability of those experiments is very poor. Several problems lead to this poor repeatability.

The lift-off process is a popular method used in university labs to pattern thin films. A good edge profile of thin films can be obtained when an anisotropic deposition or line-of-sight (e.g., thermal evaporation or e-beam evaporation) is executed on a photoresist film with an undercut profile. The sputtering process used in those experiments is not a good anisotropic deposition technique. Particles of desired materials easily adhere on the sidewall of the photoresist layer. Therefore, notches are generally formed at the edge of deposited thin film after a lift-off process, as shown in Figure 1.18a. These notches at the edge of the bottom electrodes will short the metal/dielectric/metal tunnel junctions. These notches also form at the edge of the top electrode using the same sputtering and lift-off processes. The dielectric layer covering the sidewall of the top electrode, as shown in Figure 1.18b, will impede molecules to bridge the top and bottom electrodes.

The Ni and NiFe used for electrode material is another problem. It is very difficult to keep a vacuum or a protective gas circumstance to prevent these metal materials from
oxidization during the device fabrication. Therefore, an oxide layer forms at the surface of Ni or NiFe electrodes. This oxide layer will impede molecules to attach on electrodes.

1.10 Goals of this work

The major goal of this dissertation is fabricating molecular molecular electrodes with sub-nm dimensional control with a high repeatability and study molecular conduction mechanism through the well established Au-thiol connection. The nano-gap electrodes for molecular attachment are formed at the exposed edge of metal/dielectric/metal trilayer structures. To reach this goal, two problems mentioned in Section 1.9 have to be solved. Etching processes, including dry etching and wet etching, are applied to obtain a good profile of top and bottom electrodes. Chapter 2 will introduce this part of work and show the $I$-$V$ property improvements of tunnel junctions. Pure Au is used to replace NiFe or Ni as the electrode material to eliminate the oxide layer forming on the electrode surface. This is a significant materials challenge to prepare Au/oxide/Au tunnel junctions. Due to surface energy mismatch, there is island growth instead of a continuous thin film growth of the oxide on Au electrodes. This will short with the top Au electrode easily. Chapter 3 will introduce a novel technique developed by our group to fabricate Au tunnel junctions with a lowest leakage current density in the world. Several molecules were tried to bridge the top and bottom electrodes. Control experiments and low temperature experiments were also executed to study these molecular devices. This part of work will be introduced in Chapter 4.
The nano-gap Au electrodes are also a good substrate to study photovoltaic materials in a nano-scale. It is assumed that the photovoltaic efficiency will be enhanced greatly when the travel distance of excited electron-hole pairs is less than the exciton diffusion length of the photovoltaic materials, which are mostly around 10 nm. The nano-gap Au electrodes at the exposed edge of Au/Al₂O₃/Au structures provide a way to prove this assumption. Therefore, another goal of this dissertation is studying photovoltaic properties of organic semiconductors between nano-gap electrodes. Chapter 5 will show the study of photodetectors with Au/Al₂O₃/Au/TiO₂/CuPc structures. A large photocurrent enhancement of Copper (II) Phthalocyanine (CuPc) was observed and supports our hypothesis of enhanced transport between nm-scale electrodes.

Though the multilayer electrodes produce nm-gaps between metal contacts, the overall device is micron/submicron in length depending on the resolution of photo lithography used. In our case, ~10 linear microns of junction result in a device with ~10,000 conducting molecules. The ultimate scaling of nm-scale electrodes would be to add another perpendicular direction of nm-scale patterning over the face of the multilayer electrode. This can be achieved by a shadow lithography technique in which a nanowire is placed over the edge of the junction creating a ‘shadow’ under the nanowire. Junction areas outside of the shadow can be covered with insulator, making only a nm-scale region available for molecular contact. In this case a single molecule electrode can be made using conventional deposition/patterning techniques. Our group had demonstrated the concept with a shadow line deposition with a width of 6 nm under a CNT (101). However controlled growth of nanowires in a precise location is a challenge. ZnO nanowires (NWs) are a better choice than CNTs not use as a mask because ZnO NWs can cast a straight
and uniform shadow. Chapter 6 will introduce the selective growth of ZnO NWs from the exposed edge of the Si/Al₂O₃/Si trilayer structure. The growth mechanisms on these nm-scale nucleation sites will also be discussed.
Figure 1.1. The development of the transistors per die and minimum feature size (*) over time (adapted from Intel official website http://www.intel.com/technology/mooreslaw/).
Figure 1.2 (a) An example of a rectifier molecule, (b) the calculated $I/V$ curve of the molecule in (a). Adapted from ref.\textsuperscript{[7]}. 
Figure 1.3. Chemical structures of metal terminated carbon chains with the Re(C≡C)Re unit (Molecule 1), oligomeric linear porphyrin arrays (Molecule 2 & 4), oligo(phenylene ethynylene)s (Molecule 3), and 4-(2’-methyl-4’(phenylethynyl)phenylethynyl)-1-phenylthiolate (Molecule 5) in the text.
Figure 1.4. Fabrication techniques of single molecular junctions: (a) Mechanical break junction technique and (b) Electromigration break junction technique. Adapted from Ref. [51] and Ref. [53], respectively.
Figure 1.5. Schematic drawing of (a) a metal/molecules/metal structure and (b) a metal/barrier layer/metal tunnel junction.
Figure 1.6. Electron with energy $E$ incident on a potential barrier.
Figure 1.7. Schematic energy diagram of a metal/molecules/metal structure with (a) a zero bias and (b) a bias of $V$. 
Figure 1.8. Schematic drawing of possible mechanisms for current tunneling across molecules.
Table 1.1. Properties associated with different capacitors.

<table>
<thead>
<tr>
<th></th>
<th>A (nm²)</th>
<th>d (nm)</th>
<th>C (F)</th>
<th>ΔE (eV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Nanocapacitor</td>
<td>5²</td>
<td>2</td>
<td>$1.1 \times 10^{-19}$</td>
<td>0.73</td>
</tr>
<tr>
<td>Microcapacitor</td>
<td>$10,000^2$</td>
<td>2</td>
<td>$4.4 \times 10^{-13}$</td>
<td>$1.8 \times 10^{-7}$</td>
</tr>
</tbody>
</table>
Figure 1.9. Schematic energy diagram of a general barrier in dielectric layer between two metal electrodes. Adapted from Ref. 66.
Figure 1.10. Coulomb blockade effect in a nano-scale capacitor.
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Figure 1.12. Equivalent circuit of metal/single molecule/metal structure connecting to a voltage source.
Figure 1.13. Coulomb blockade effect in a double junction system. $V_f = e/(2C)$. 
Figure 1.14. Equivalent circuit of a single molecular transistor.
Figure 1.15. Coulomb diamond structures for a single molecular transistor. $V_1 = e / 2C_g$. 
Figure 1.16. Donor and acceptor materials used in organic solar cells.
Figure 1.17. Schematic drawing of the fabrication steps: (a) deposition of a bottom electrode, (b) deposition of an alumina insulating layer and a top electrode, and (c) a molecular attachment at the exposed edge of a metal/dielectric/metal junction.
Figure 1.18. Schematic drawing of the formation of notches at the edge of (a) the bottom electrode by a lift-off process and (b) the top electrode and insulator length exceeding molecule length to prevent molecular bridging.
Chapter 2

Fabrication development of nano-gap electrodes at the exposed edge of

Metal/Al₂O₃/Metal trilayer structures (Metal = NiFe & Ni)

2.1 Introduction

The photolithography and lift-off processes to fabricate molecular devices \(^{(100)}\) will generate notch defects at the edge of thin films. These notches will be short tunnel junctions with top deposited electrode or block molecular attachment because the top layer can be far removed (>100nm) from the bottom. In order to eliminate these notches and obtain reliable metal/dielectric/metal tunnel junctions, a new photolithography technique, wet etching, and dry etching were tried. In this chapter, all technique developments will be introduced step by step following the fabrication flow: (1) a new pattern design for both top and bottom electrodes, (2) wet etching for bottom electrodes, (3) double-photoresist (PR) photolithography, (4) dry etching of the dielectric layer, (5) the sacrificial layer.

2.2 Fabrication development

2.2.1 Pattern design
Figure 2.1a shows the top view of the old pattern design for molecular devices. The horizontal lines are top electrodes and the vertical lines are bottom electrodes. The line width is 5 μm and the square pad area is $1\text{mm} \times 1\text{mm}$ designed for probe contact. A large amount (36) of tunnel junctions can be fabricated on a piece of Si chip. However, the $I-V$ properties of each tunnel junction are easily affected by the surrounding tunnel junctions if shorts or broken lines are present. To solve this problem, a new pattern of separated tunnel junctions was designed, as shown in Figure 2.1b. There are 16 separated tunnel junctions on a piece of Si chip. Figure 2.2b only shows one quarter of the total pattern. This new pattern was applied for device fabrication from Sample No.91.

2.2.2 Bottom electrodes by wet etching

2.2.2.1 Experimental details

Two samples were prepared using different methods in this work. Figure 2.2 shows the whole fabrication process for both samples. Sample A was prepared following procedures in Ref.\textsuperscript{(100)}, in which both electrodes were fabricated by photolithography, film deposition, and lift-off processes. First, a Si wafer with a 100 nm SiO\textsubscript{2} layer was ultrasonically cleaned with acetone, isopropanol (IPA), deionized (DI) water, and nitrogen drying. A normal one layer photolithography method was applied to pattern the bottom electrode using Shipley 1813 positive photoresist at a Karl Suss mask aligner. An AJA International Sputtering system was used to deposit Co and NiFe films, respectively. The deposition condition is at 1 mTorr with a gun RF power of 150 W. Then, a lift-off step was executed to define the bottom electrode pattern via Shipley 1165 resist remover for 3
h. The top electrode (NiFe) was fabricated across the bottom electrode using a same process mentioned above. Before the top electrode deposition, an Al₂O₃ dielectric layer with a thickness of 2 nm was deposited. This Al₂O₃ dielectric layer was fabricated using a specific process. An Aluminum layer of 1 nm was first sputtered on the bottom electrode at 2 mTorr with a gun DC power of 75 W. A gas mixture of Ar and O₂ (1:1) was flowed into the chamber and ignited at 60 mTorr with a 20 W bias power for 30 s to oxidize the Al layer. Then, a second Aluminum layer of 0.5 nm was sputtered and oxidized to form a final alumina layer of 2 nm. After getting tunnel junctions with a structure of Co 5 nm/NiFe 10 nm/Al₂O₃ 2 nm/NiFe 10 nm, the sample was put in a quartz tube. The tube was purged by an Ar flow for 30 min first and heated with a rate of 10 K/min. After the sample was annealed in the Ar flow at 453 K for 60 min, the tube was cooled down with a rate of 10 K/min.

Wet chemical etching was used to replace the lift-off to prepare the bottom electrode in sample B. The Co and NiFe film was first sputtered on the SiO₂ wafer, sequentially. Photoresist was patterned on the NiFe film and the sample was immersed in a 0.2 M HCl solution for 5 min to etch the Co/NiFe film. The bottom electrode formed after removing the remaining photoresist. The patterning of the dielectric layer and top electrode is same as that of sample A.

The $I$-$V$ properties were characterized by an MM Micromanipulator probe station. AFM images and measurements were gathered with a PicoPlus AFM system (Molecular Imaging, Agilent Technologies).

2.2.2.2 Results and discussion
Sample A and B both show good performance as tunnel junctions after annealing (see Figure 2.3). A reduction of defects in the Al$_2$O$_3$ layer by the annealing process improves the insulating property of tunnel junctions. There are 16 isolated tunnel junctions in each sample. The current of tunnel junctions of sample A is $(10.0 \pm 1.0) \times 10^{-7}$ A at 0.1 V and that of sample B is $(5.0 \pm 1.0) \times 10^{-7}$ A at the same applied bias. 10 tunnel junctions were measured for each sample. This result shows that the etching process to form the bottom electrode, without jagged tears from liftoff process, results in improved junction quality.

Simmons model and Brinkman model (102) were used to fit the effective barrier thickness and barrier height of the alumina insulating layer. It is very clear from Figure 2.4 that sample B has a smaller deviation of the barrier thickness and barrier height than sample A. The barrier thickness of sample B is about 19 Å, which is consistent with the physical thickness of the alumina layer measured by AFM (~20 Å).

The yield of sample B (etched) is 98% for 400 tunnel junctions, that is much higher than the 15% yield of sample A. This high yield of sample B confirms that this wet etching process to pattern the bottom electrodes is an improved method for molecular device fabrication. The break down voltage of tunnel junctions of sample B is 2.7~3.2 V, higher than 1.5~2.0 V of sample A, as shown in Figure 2.5.

AFM is a very good tool to study the morphology of the bottom electrodes for both liftoff and wet etched samples. The 3D AFM images in Figure 2.6 show many notches ~50 nm tall formed at the edge of the bottom electrode in sample A that can electrically short with the top electrode deposited later. There are no notches observed at the edge of the bottom electrode in sample B. These notches in Figure 2.6a leads to a high probability to short
tunnel junctions. This is the reason why sample A has a low yield below 15% and a small break down voltage of 1.5~1.8V.

The wet chemical etching process does not produce notches and improves the electrical performance of Co 5 nm/NiFe 10 nm/Al₂O₃ 2 nm/NiFe 10 nm tunnel junctions greatly. The high yield of ~ 98% (400 tunnel junctions) and the low cost of this technique indicate this wet etching method as an excellent way to fabricate molecular devices.

2.2.3 Patterning top electrodes by a double-PR photolithography

In order to obtain a uniform edge profile of top electrodes and prevent the situation depicted in Figure 1.18b, several fabrication routes were explored based on equipment available in the Center for Nanoscale Science and Engineering (CeNSE).

Wet etching was tried first to fabricate top electrodes. The insulating layer thickness of 2 nm was found too small to prevent the acid from etching bottom electrodes. Therefore, most of bottom electrodes were observed to be etched after device fabrication.

In the semiconductor industry, reactive ion etching (RIE) is commonly used to pattern thin films. Chlorine-based plasmas \(^{(103)}\) are used to etch metal films. Unfortunately, the RIE system (Plasmalab 80) in CeNSE is designed to etch Si & SiO₂ and the chlorine gas is not allowed to use. Thus physical ion ablation with the Ar milling process was executed to etch the Ni film following a PR mask. Results show that the etching efficiency of Ni compared to PR by Ar milling was too small. The PR mask was totally removed before the Ni film was etched. Another problem is the polymer residue of PR
after Ar milling. Various PR removers and the O₂ plasma ashing process were tried to remove the polymer residue. All of these procedures did not work well.

Therefore, the only available method is the photolithography + lift-off method. As mentioned above, notches form at the edge of thin film by a common photolithography + lift-off route. Here, a double-PR-layer photolithography is introduced to obtain good metal patterns as depicted in figure 2.7. The overhanging top PR layer prevents side wall deposition during metal evaporation, and hence a ‘clean liftoff’ when PR is removed by stripper. A Si wafer with a 100 nm SiO₂ layer is ultrasonically cleaned by acetone, isopropanol (IPA), deionized (DI) water, and nitrogen drying. A layer of PMGI (MicroChem) polymer was first spin coated on the Si wafer and baked at 170°C for 5 min. A layer of S1813 (MicroChem) was spin coated on the PMGI layer and baked at 115°C for 1 min. Then, the Si wafer was exposed in a UV light for 10s at a Karl Suss mask aligner. The double layer PR was developed in a MF-319 (Microposit) solution for 5~10 min. A good undercut structure of the PMGI/S1813 double layer formed, leading to a Ni top line without any edge notches, as shown in Figure 2.7a. Figure 2.7b is the top view of the undercut structure. The open line width of S1813 is 5μm and that of PMGI is ~ 9 μm. Figure 2.7c is the top view of a single developed S1813 layer using the same photomask in Figure 2.7b. The horizontal lines in Figure 2.7b&c are the bottom Au & NiFe electrodes, respectively.

2.2.4 Dry etching of the dielectric layer
The alumina insulating layer and the top electrode layer were deposited together by a single-layer-photolithography in the previous work \(^{(100)}\). To meet the vertical sidewall of the insulating layer and top electrode in Figure 1.17b, Ar milling was used to open the alumina insulating layer after patterning the top electrode.

### 2.2.5 The sacrificial layer

It was found that the Al\(_2\)O\(_3\) insulating layer was etched during the photolithography process for patterning top electrodes. The PR developer (MF-319, Microposit) is a basic solution and would like to react with the Al\(_2\)O\(_3\) layer. To solve this problem, a sacrificial Ni layer was deposited on the Al\(_2\)O\(_3\) layer to inhibit the etching issue.

### 2.3 Final fabrication flow

Figure 2.8 shows the whole fabrication process for the nano-gap electrodes at the exposed edge of metal/Al\(_2\)O\(_3\)/metal trilayer structures (metal = NiFe & Ni). The bottom electrodes were prepared by photolithography and wet etching. This part has been introduced in Section 2.3 in detail. After patterning the bottom electrode, an Al\(_2\)O\(_3\) layer of a 2 nm thickness was deposited by Al sputtering and O\(_2\) plasma oxidation. Then, a sacrificial metal layer of a 2 nm thickness was sputtered on the Al\(_2\)O\(_3\) layer in the same AJA International Sputtering system to protect the Al\(_2\)O\(_3\) layer from the PR developer etchant. After a good undercut profile formed, a metal layer of a 20 nm thickness was e-beam evaporated to pattern the top electrode at a Torr International EB4P series system. A second lift-off process was executed to remove PR. The top electrode left has a vertical
sidewall profile and works as an etch mask for the following Ar milling. The structure of the exposed edge of metal/Al$_2$O$_3$/metal multilayer structure was obtained after the Ar milling process at Plasmalab 80 stopped on the metal bottom electrode. The gap between the top and bottom electrodes is precisely controlled by the thickness of the Al$_2$O$_3$ layer. The gap scale can reach 2 nm. Therefore, molecules larger than 2 nm can bridge these two electrodes to form a molecular device.

Sample No.141 & 146 were prepared using this new fabrication flow and act as representative samples. The sacrificial Ni layer is 10 Å for both samples. The only difference between these two samples is the thickness of the Al$_2$O$_3$ insulating layer. Sample No.80 was prepared using the old method$^{(100)}$ for a comparison. All $I$-$V$ measurements were performed at room temperature by a Keithley 2430 1KW Pulse Sourcemeter, a Keithley 6430 Sub-femtoamp Remote Sourcemeter, and an MM Micromanipulator probe station.

2.4 Electrical properties

The tunneling current densities (TCD) of the nanogap electrodes at the exposed edge of NiFe/Al$_2$O$_3$/Ni tunnel junctions are shown in Table 2.1. The thickness of the Al$_2$O$_3$ layer and the Ni layer was measured by AFM. Sample No.141 has a TCD of ~ 0.0015 A/cm$^2$. Sample No.146 has a TCD of ~ 15 A/cm$^2$. They are both far smaller than the TCD of ~ 300 A/cm$^2$ of Sample No.80 fabricated by the lift off process$^{(100)}$ process.

Figure 2.9a shows the current density-voltage characteristics of Sample No.141 and Sample No.146. Both charts show a typical tunneling character. The current density-
voltage curve of sample No.141 was fitted by Simmons model. A barrier height of 1.0 eV and a barrier thickness of 28.4 Å were obtained. The simulated Al₂O₃ layer thickness is larger than the AFM measurements of 20 Å. One possible explanation is the sacrificial Ni layer partially or fully oxidized. Ni has a large work function (5.01eV) approaching that of Au (5.1 eV) and XPS studies have shown that an oxide free surface can exist \(^{(104)}\). However, under the handling conditions required for chemical modification, it is possible that an oxide surface layer forms making direct molecular attachment to metal electrode difficult. To test this hypothesis, a reference sample of a 10 nm Ni film was exposed in the air for 10 min. Then it was scanned at a Spectroscopic Ellipsometers (M-2000V, J.A.Woollam Co. Inc.) and a thin NiO layer of a 7 Å thickness was detected. Therefore, the total oxide layer thickness should be 20 Å + 7 Å = 27 Å. This is consistent with the simulated barrier thickness of 28.4 Å by Simmons model. Another control experiment was done by changing the Al₂O₃ thickness from 20 Å (sample No. 141) to 10 Å (sample No.146). The total oxide layer thickness should be 17 Å. And this is also consistent with the simulated barrier thickness of 18.1 Å derived from Figure 2.9b. These results confirm the sacrificial Ni layer partially oxidized. The dielectric thickness of 17~18 Å in Sample No.146 is smaller than that of 20 Å in Sample No.80. However, the tunneling current density of 15 A/cm² in Sample No.146 is 20 times smaller than that of 300 A/cm² in Sample No.80 (lift off process). These comparisons shows tunnel junctions fabricated by the etching process to define top and bottom electrode lines have much better insulating properties than those fabricated by the process of liftoff with torn edges.

2.5 Molecular attachment
A ~ 30Å long organometallic cluster (OMC) with thioacetate terminated tethers was first synthesized\textsuperscript{(105)} by D.F. Li \textit{et al.} to bridge the nanogap electrodes. The chemical formula of the OMC is \[(pzTp)\text{Fe}^{\text{III}} (\text{CN})_34 \ [\text{Ni}^{\text{II}}(L)]_4[\text{O}_3\text{SCF}_3]_4 \ [(pzTp) = \text{tetra(pyrazol-1-yl)borate}; L = 1-\text{S(acetyl)}\text{tris(pyrazolyl)}\text{decane}] \ (\text{Molecule I}).\] Figure 2.10 shows its X-ray structure. This molecule essentially comprises a cube of 12 edges of cyanide bridged Ni and Fe atoms (-Ni-N≡C-Fe-). There are four 10 carbon alkane tethers connecting 4 Ni atoms at the alternating corners of the molecular cube\textsuperscript{(105)}. The thioacetate group is a protecting group to preclude thiol reactions during the formation of an octametallic core. This thiolacetate group is readily removed during an electrochemical molecule attachment\textsuperscript{(106)} process on the device to form thiol-metal (metal = Ni or NiFe) surface bonds.

Another similar OMC (Molecule II) was also synthesized for molecular attachment. The only difference between Molecule I and Molecule II is the L part in the chemical formula. The acetyl group is replaced by the hydrogen atom (thiol) in Molecule II for easy attachment on the metal surface without electrochemical activation.

To attach Molecule I with thioacetate ligand to the Ni electrodes, a 2mM solution of OMC in a dichloromethane (CH$_2$Cl$_2$) solvent was subjected to an alternating ±100mV biasing between two metal electrodes. The time interval was 0.02s and lasted for 2 min. After the molecular attachment process completed, the sample was sequentially cleaned with IPA, DI water, and nitrogen drying. To attach Molecule II to metal electrodes, the nano-gap electrode was immersed in a same 2mM solution of OMC in a CH$_2$Cl$_2$ solvent for 2 min. Then the sample was sequentially cleaned with IPA, DI water, and nitrogen drying. Electrical properties of tunnel junctions before and after molecule attachment
were performed by the Keithley 2430 1KW Pulse Sourcemeter, the Keithley 6430 Sub-femtoamp Remote Sourcemeter, and the MM Micromanipulator probe station.

Unfortunately I-V studies show no difference before and after molecule attachment. This indicates the current is not passing through molecules. Over 1,000 working tunnel junctions with NiFe/Ni electrodes had been tested before and after Molecule I/II attachment. Figure 2.11 shows the current-voltage characteristics of a representative sample (No.146) before and after molecular attachment. There is no current increase due to molecular attachment, considering the I-V measurement variation. 150 junctions done with conditions the same as No.146 did not show molecular current increases. The electrode gap of ~ 17 Å in Sample No.146 is smaller than the OMC length allowing molecules to bridge the top and bottom electrodes but no molecular current was detected.

Since a nickel oxide layer of 7~8 Å has been measured by the ellipsometer measurement and by Simmons tunnel current simulation in Section 2.4, it is likely that oxide layers on the surface of both Ni electrodes blocks the bonding between the thiol group of molecule and metal atom. In the prior report from this group (100), dichloromethane was used as a solvent for the electrochemical addition of the thioacetate functionalized molecule. Exposure to air produces HCl in the dichloromethane and it was postulated that this acid helped etch NiO to give a clean surface. However over etching would result in shorts between electrode layers or complete etching of metal lines. The dichloromethane would evaporate during the functionalization process thereby concentrating acid. This would make etching conditions extremely difficult to reproduce. After over 3000 tunnel junctions were made and tested, working directly and independently of Tyagi, I found no conclusive molecular current was seen that could not be explained as an electrode short.
Therefore, a noble metal should be used to replace Ni/NiFe as the electrode material to test the nanogap electrode structure and study molecular current through the metal complex. Much of the molecular electronics literature to date has utilized Au-thiol chemistry to ensure clean inert surfaces for controlled molecular contacts. Therefore, fabrication of gold tunnel junctions is required. It needs to be pointed out that because insulators do not form stable films on Au, this requires an innovative fabrication approach that will be introduced in the following chapter.
Figure 2.1. Schematic drawing of the top view of the (a) old and (b) new pattern design for both electrodes. The sizes of the square pads and lines in (a) & (b) are 1mm×1mm, 2μm×2mm, and 5μm×1.5mm, respectively.
Figure 2.2. Schematic drawing of the fabrication process of (a) the bottom electrode by a lift-off process, (b) the bottom electrode by a wet etching process, and (c) the top electrode by a lift-off process. The bottom electrodes of Sample A and B was fabricated following (a) and (b) route, respectively. The top electrode of both samples was fabricated following route (c).
Figure 2.3. Current versus voltage behavior of the Co/NiFe/Al$_2$O$_3$/NiFe electrode fabricated by the lift-off (sample A) and wet chemical etching (sample B) before and after annealing.
Figure 2.4. Barrier thickness and barrier height of tunnel junctions fabricated by the lift-off (Δ, sample A) and the chemical wet etching (♦, sample B) with Simmons & Brinkman models (10 tunnel junctions measured for each sample).
Figure 2.5. Break down voltage of tunnel junctions fabricated by a lift-off process (sample A) and a chemical wet etching process (sample B).
Figure 2.6. 3D AFM images of the bottom electrode in (a) sample A by a lift-off process and (b) sample B by a wet chemical etching process.
Figure 2.7. (a) Schematic drawing of the Ni top electrode by an S1813/PMGI undercut profile. Microscope top view images of (b) an S1813/PMGI-double-layer undercut profile and (c) an S1813-single-layer profile.
Figure 2.8. Schematic drawing of the nanogap electrode fabrication at the exposed edge of metal/Al₂O₃/metal trilayer structures (metal = NiFe & Ni).
Table 2.1. The barrier thickness and tunneling current density comparison of Metal/Al₂O₃/Metal structures by different fabrication routes (Metal = NiFe & Ni).

<table>
<thead>
<tr>
<th>Sample</th>
<th>Structure</th>
<th>Tunneling current density (A/cm²)</th>
<th>Fabrication route</th>
</tr>
</thead>
<tbody>
<tr>
<td>No.80</td>
<td>NiFe/Al₂O₃ 20 Å/Ni</td>
<td>~ 300</td>
<td>Ref. [100]</td>
</tr>
<tr>
<td>No.141</td>
<td>NiFe/Al₂O₃ 20 Å/Ni 10 Å/Ni</td>
<td>~ 0.0015</td>
<td>This work</td>
</tr>
<tr>
<td>No.146</td>
<td>NiFe/Al₂O₃ 10 Å/Ni 10 Å/Ni</td>
<td>~ 15</td>
<td>This work</td>
</tr>
</tbody>
</table>

Note: The tunneling current densities of all samples were measured at 0.5 V.
Figure 2.9 Current density-Voltage characteristics of NiFe/Al₂O₃/Ni tunnel junctions with exposed side edges (■) and Simmons simulation (▬). The thickness of Al₂O₃ is 20 Å (a) and 10 Å (b). The barrier thickness of the simulation curves of (a) and (b) are 28.4 Å and 18.1 Å, respectively. A barrier height of 1.0 eV is used for both simulations.
Figure 2.10. X-ray structure of the organometallic cluster \([(pzTp)Fe^{III}(CN)_3]_4\) 
\([Ni^{II}(L)]_4[O_3SCF_3]_4\) \([(pzTp) = \text{tetra(pyrazol-1-yl)borate}; L = 1-S(\text{acetyl})\text{tris(pyrazolyl)decane}].\) All anions, hydrogen atoms, pendant pyrazoles, and disordered S(\text{acetyl})hexyl- chains are removed for clarity \[105\].
Figure 2.11. Current-Voltage characteristics of bare NiFe/Al₂O₃/Ni tunnel junctions before and after Molecule I & II attachment.
Chapter 3

Nano-gap electrodes formed at the exposed edge of Au/SAM/Al₂O₃/Au tunnel structures grown by atomic layer deposition

3.1 Introduction

Fabrication of nanometer-scale electrode gaps is a critical step for numerous devices based on molecular conduction and to probe the fundamental transport properties of molecular materials such as organic conductors. Many techniques have been developed to generate nano-gaps between electrodes in which molecules are bridging. They can be divided into the line-gap (51–54, 58–60, 107), cantilever-tip-gap (9, 43, 50, 108, 109) and plane-gap techniques (40, 41, 45, 47, 65, 100, 110, 111). Nano-gaps fabricated by the line-gap technique are formed in the middle of a metal line, which is composed of pure Au only. Several techniques such as mechanical break junction (51, 52), electromigration junction (53, 54, 58, 107), tip-end junction (59) and shadow lithography junction (60) have been well developed to realize nano-gap electrodes for studying molecules, even for single molecules but suffer from scaling and yield issues. Scanning probe microscopy (SPM) is a tool used normally to measure the morphology of the self-assembled monolayer (SAM) of molecules on the metal surface (30, 43, 50, 108, 109) and produce a nm-scale cantilever-tip-gap. This technique simplifies the fabrication process and eliminates the problem of shorting however the single probe limits its application in devices.
The plane-gap techniques use a metal/insulator/metal structure to create nano-scale gaps relying on the thickness of the insulator to set the critical electrode gap between metal electrodes. Several techniques including Langmuir-Blodgett (LB) film\(^{(40, 41)}\), nanopore\(^{(47)}\), crossing metal wires\(^{(65)}\), and hanging Hg drop electrode\(^{(45)}\) have been developed to attach molecules between plane electrodes while those devices typically suffer from electrode shorting problems. Recently, several groups concurrently developed a simple technique to fabricate the exposed edge of metal/oxide/metal structure for molecular electrodes\(^{(100, 110, 111)}\). This technique uses highly controllable film thickness (i.e. Al\(_2\)O\(_3\)) to set the critical spacing between electrodes. After lift-off or etching process, molecule clusters can bridge across the nm-thick insulator connecting top and bottom metal contacts\(^{(100)}\). The critical challenge of this device design is to have a high quality insulator film since background tunnel current can dominate device current instead of the conduction through molecules bridging between electrodes at the edge. The system, with NiFe or Ta metal contacts, also possessed long term stability issues due to surface oxidation and hillock formation from stress release\(^{(112, 113)}\) and eventual surface oxidation of metal surface. Much of the molecular electronics literature to date has utilized Au-thiol chemistry to ensure clean inert surfaces for molecular contacts. However it is difficult to form stable Au-oxide tunnel junctions due to a high surface energy mismatch, subsequent island growth of oxide and the formation of shorts. It has previously been observed that SAMs can aid in uniform Au deposition on SiO\(_2\) substrate that usually require a reactive metal wetting layer (i.e. Ti)\(^{(114)}\). Although Au-oxide tunnel junction can be fabricated when the oxide layer is thick enough to coalesce from islands to a continuous film, it is extremely difficult to fabricate high quality Au tunnel junctions...
when the thickness of the oxide insulating layer is below 5 nm. Until now, Au tunnel junctions with an oxide insulating layer have rarely been reported. J.S. Moodera et al.\textsuperscript{(115)} cryogenically deposited Al\textsubscript{2}O\textsubscript{3} between Au layers and the $dI/dV$ vs voltage curve demonstrates typical tunneling characters but Al\textsubscript{2}O\textsubscript{3} thickness was not mentioned. G.J. Ashwell et al.\textsuperscript{(111)} realized Si\textsubscript{3}N\textsubscript{4} deposition on Au with a SiO\textsubscript{2} mushroom-shaped dome to form Au/ Si\textsubscript{3}N\textsubscript{4}/SiO\textsubscript{2}/Au structure with a nano-gap over 3.5 nm which can only be applied to study very large molecules.

In this work, we employed atomic layer deposition (ALD) to grow Al\textsubscript{2}O\textsubscript{3} layer on Au electrodes that were modified with a SAM of alcohol groups. The alcohol provides a hydrogen source for the monolayer reaction with trimethyl aluminum thereby giving uniform coverage. Ar milling was then used to expose the edge of the Au/insulator/Au structure which has a much lower leakage current density than those Au tunnel junctions previously reported. The gap between two Au electrodes below 2 nm was realized and is thus suitable for the study of small molecule conduction.

\subsection*{3.2 Experimental details}

The structure of the nanogap on the exposed edge of Al/Au/SAM/Al\textsubscript{2}O\textsubscript{3}/Au multilayer is schematically shown in Fig.3.1a. The whole fabrication flow was schematically drawn in Fig.3.2. The device fabrication started with a 1000 Å thick SiO\textsubscript{2} layer grown thermally on Si substrate sequentially cleaned with acetone, deionized (DI) water and nitrogen drying. The bottom electrode was lithographically patterned (Karl Suss MJB3, S1813/PMGI-SF11 resist) into microwires connecting to large area pads ($\sim 1 \times 1 \text{ mm}^2$) for electrical
probing in a microprobe station. Onto this 50 Å of Al and 500 Å of Au were sputter coated (AJA systems) and the bottom electrode pattern realized by liftoff. Then the bottom electrode was dipped into 10 mM β-mercaptoethanol (HSCH₂CH₂OH, Sigma-Aldrich, ≥ 99%) solution for 30 min to form a self-assembled monolayer on Au surface to provide –OH groups for the following atomic layer deposition of Al₂O₃ (Cambridge Nanotech Savannah 100 system). 14, 18 and 23 deposition cycles (H₂O/trimethyl aluminum) were applied for sample No. 333, No. 328 & No. 374, respectively. In order to protect Al₂O₃ material from being etched by the alkaline photoresist developer, 200 Å of Au was sputtered on the Al₂O₃ ALD layer. The top Au electrode (~800 Å) was formed by thermal deposition into lithographically patterned top electrodes followed by liftoff and works as the top etch mask for the following Ar milling. The structure of the exposed edge of Au/SAM/Al₂O₃/Au multilayer (Figure 3.1) was obtained after the Ar milling process (Plasmalab 80) stopped on the Au bottom electrodes.

I-V curves of Al/Au/SAM/Al₂O₃/Au structure with exposed side edges of different Al₂O₃ layer thickness were performed at room temperature by the Keithley 2430 1KW Pulse Sourcemeter or 6430 Sub-femtoamp Remote Sourcemeter and MM Micromanipulator probe station. Atomic force microscope (AFM) measurements were made by the PicoPlus AFM system (Molecular Imaging, Agilent Technologies) and Scanning electron microscope (SEM) images were recorded using a Hitachi S4300 system. The Al₂O₃ film thickness was confirmed by Spectroscopic Ellipsometers (M-2000V, J.A.Woollam Co. Inc.).

3.3 Results and discussions
SEM images of a cross junction of Al 5 nm/ Au 50 nm/SAM/Al₂O₃ 2 nm/Au 50 nm multilayer structure (sample No.328) are shown in Figure 3.1b and 3.1c. Two perpendicular metallic microwires are separated at the junction site by the SAM/Al₂O₃ insulating layer with a combined thickness of 2-3 nanometer. The bottom electrode, deposited by sputtering, has a width ~10 μm and the top electrode, deposited by thermal evaporation, has a width ~7.5 μm with a sharp edge produced by Ar ion milling. The uniformity of the edge profile is significantly improved compared to metal/insulator/metal structures using lift-off process (100, 110). The top Au electrode is composed of two layers which can be seen in Figure 3.1c. The upper layer is the Au etch mask that was defined by photolithography and liftoff. The top layer of the electrode acts as an Ar milling etch mask with its thickness reduced 800 Å to ~ 300 Å, as confirmed by AFM measurement. The lower layer of the top Au electrode is deposited over the entire Al₂O₃ sample area to protect the Al₂O₃ insulating layer from being etched away by the alkaline photoresist developer (used to define the upper layer of the top electrode pattern) and has a thickness of 200 Å. Outside of the top Au layer etch mask, the Ar milling step etches through the lower layer Au, Al₂O₃ and SAM layers to form the electrode structure diagrammed in Figure 3.1a. In our system the etching of Al₂O₃ was significantly slower than Au, requiring the relatively thick Au etch mask and end points were calculated from etch rate calibrations immediately prior to etch runs.

Figure 3.3 shows the typical tunneling characters of Al/Au/SAM/Al₂O₃/Au structure with exposed side edges of different Al₂O₃ layer thickness, indicating good insulating property of SAM/Al₂O₃ layer between Au electrodes. The Al₂O₃ layer thicknesses of sample No.333 and No.328 are 15.4 Å and 19.9 Å, respectively, which were confirmed
by the Spectroscopic Ellipsometer. This measurement is consistent with alumina ALD deposition cycles of sample No.333 and No.328 (14 and 18, respectively). The I-V curves in Figure 3.3 are fitted by Simmons model \(^{(66)}\) to obtain their barrier thickness \(s\) (nm) and height \(\phi\) (eV). I-V characteristics of sample No.328 were fit by Simmons model to obtain the barrier thickness (23.7 ± 0.4 Å) and barrier height (~ 1.2 eV), which is significantly less than the commonly observed barrier height of ~ 3 eV for Al\(_2\)O\(_3\) layers \(^{(116,117)}\) using similar alumina ALD deposition method. This is possibly due to the imperfect bonding of Al\(_2\)O\(_3\) with HSCH\(_2\)CH\(_2\)OH, rough morphology of the sputtered Au substrate and the additional β-mercaptoethanol layer decreasing the net barrier height of SAM/Al\(_2\)O\(_3\) structure. The same procedures were carried out for sample No.333 & No.374 to acquire the barrier thickness of 19.8 ± 0.6 Å and 29.0 ± 0.2 Å, respectively, using the same barrier height. The thickness of β-mercaptoethanol layer can be estimated by subtracting Al\(_2\)O\(_3\) layer thickness (ellipsometer) from the total barrier thickness. Results in Table 1 show 4.4 ± 0.6 Å for sample A and 3.8 ± 0.4 Å for sample B, which are consistent with the typical thickness (3.5-5.0 Å) of β-mercaptoethanol monolayer on Au (111) surface \(^{(109,118)}\). When the Al\(_2\)O\(_3\) layer becomes thicker as in sample C, it becomes difficult to estimate the SAM thickness (by subtraction) with the oxide dominating overall tunnel current.

Comparison of the junction tunneling properties of this work to other metal tunnel junctions, having similar exposed edge structures, is listed in Table 3.2. Sample No.333 has a tunneling current density (0.20 ~ 0.75) A/cm\(^2\) at 0.5 V, which is over 1 order of magnitude smaller than 10 ~ 20 A/cm\(^2\) of NiFe/Al\(_2\)O\(_3\)/NiFe structure at the same thickness and applied voltage \(^{(100)}\). Sample No.328 has a tunneling current density (3.4 ~
8.6)×10⁻³ A/cm² at 0.5 V with a gap of 23.7 ± 0.4 Å and sample No.374 has a tunneling current density (1.4 ~ 2.3)×10⁻⁵ A/cm² at 0.5 V with a gap ~ 30 Å, which is over 2 orders of magnitude smaller than the literature precedence of ~ 6×10⁻³ A/cm² for the Pt/Al/AlOₓ(> 30 Å)/Pt structure at 0.5 V (110) and Au/Si₃N₄(35 Å)/SiO₂/Au structure at 0.3 V (111). This illustrates that ALD of an Al₂O₃ layer on Au/SAM substrate results in a marked improvement in Au-insulator quality.

AFM images of Au film and Al₂O₃ layer on different substrates are shown in Figure 3.4. In general, the surface roughness of noble metal substrate plays a critical role in determining the quality of the insulating layer and device properties (110). The root mean square (rms) roughness of about 0.5 nm for a 20 nm thick Au film on Si/SiO₂/Al (5 nm) substrate is achieved by careful sequential deposition of aluminum and gold film without any break from vacuum (base pressure ~5×10⁻⁸ torr). The sample topography remains similar and its rms roughness varies between 0.5 and 0.6 nm during the fabrication process of Al/Au/SAM/Al₂O₃/Au structure, which can be observed from Figure 3.4a-c. This confirms that a uniform coating of both β-mercaptoethanol and aluminum oxide layers are on the Au substrate. The conformal nature of the SAM and ALD process also allows good tunnel barrier properties even on top of a rough Au films (rms ~ 2 nm) deposited by a fast thermal evaporation process. As a control experiment, an Al₂O₃ film was grown directly on Au bottom electrode (rms ~ 0.5 nm) without SAM treatment (Si/SiO₂ /Al 5 nm/Au 50 nm/ Al₂O₃ 2 nm/Au 50 nm). The surface topography for the untreated Au becomes markedly worse with the rms roughness increasing to 0.9 nm, as shown in Figure 3.4d. The morphology results in a very high current density ~ 10³ A/cm² consistent with electrical shorting.
The topography of different layers in Figure 3.4 also proves the critical role of the β-mercaptoethanol SAM structure in working Au tunnel junctions. The original Au substrate has a grain size of 30 ~ 50 nm and an average grain height smaller than 3 nm in Figure 3.4a. A uniform monolayer of HSCH$_2$CH$_2$OH covered the Au substrate and the following Al$_2$O$_3$ ALD growth keeps a similar topography as the Au substrate. Figure 3.4b & 3.4c shows the same window of grain size (30 ~ 50 nm). This process is schematically drawn in Figure 3.5a. However, Al$_2$O$_3$ growth changes from a layer growth on HSCH$_2$CH$_2$OH SAM structure to an island growth when Al$_2$O$_3$ is deposited on the Au film directly. The Al$_2$O$_3$ thickness (~2 nm) is comparable to the grain height (0.5 ~ 3 nm) of the Au substrate. Therefore, some ‘low’ grains disappear and some ‘high’ grains grow after a random distribution of Al$_2$O$_3$ islands (see Figure 3.5b). A large distribution of grain sizes (30 ~ 100 nm) and a high rms roughness (0.9 nm) was observed for the Al 5 nm/Au 20 nm/Al$_2$O$_3$ 2 nm structure in Figure 3.4d.

3.4 Conclusions

Au tunnel junctions of Al/Au/SAM/Al$_2$O$_3$/Au structure were achieved by atomic layer deposition of Al$_2$O$_3$ onto HSCH$_2$CH$_2$OH SAM on an Au bottom electrode. The alcohol terminated SAM acts to grow a conformal monolayer of Al$_2$O$_3$ from trimethyl aluminum. The nano-gaps formed at the exposed edge of Au/SAM/Al$_2$O$_3$/Au structure can be as thin as 20 Å with a barrier height of ~ 1.2 eV, which makes them excellent candidates for molecular conduction studies. In particular, the conduction mechanisms of ferromagnetic cluster compounds with thiol terminated linkages can be studied with inert Au electrode contacts. One to three orders of magnitude reduction in background tunnel current
density are seen compared to related junctions enabling higher performance molecular junctions.
Figure 3.1. (a) Schematic 3D view and (b, c) SEM images of Al 5 nm/Au 50 nm/SAM/Al₂O₃ 2 nm/Au 50 nm (sample B) used in this study (scale bar 10um). (c) expanded magnification the circle area in (b), scale bar 250 nm.
Figure 3.2. Schematic drawing of the nanogap electrode by the exposed edge of Al/Au/SAM/Al₂O₃/Au multilayer.
Figure 3.3. $I$-$V$ characteristics of Au/SAM/Al$_2$O$_3$/Au tunnel junctions with exposed side edges (■) and Simmons simulation (▬). The thickness of Al$_2$O$_3$ is 15.4 Å (a), 19.9 Å (b) and 27.3 Å (c). The barrier thickness of the simulation curves of (a), (b) and (c) are 19.4 Å, 23.4 Å and 29.0 Å, respectively. A barrier height of 1.2 eV is used for all simulations.
Table 3.1. ALD grown cycles, measured Al₂O₃ layer thickness by ellipsometer, calculated barrier thickness by Simmons simulation and calculated HSCH₂CH₂OH layer thickness of Au/SAM/Al₂O₃/Au structure. Barrier heights of all samples were 1.2 eV by Simmons fit.

<table>
<thead>
<tr>
<th>Sample No.</th>
<th>ALD grown cycles</th>
<th>Al₂O₃ layer thickness by ellipsometer</th>
<th>Barrier thickness by Simmons simulation</th>
<th>HSCH₂CH₂OH layer thickness</th>
</tr>
</thead>
<tbody>
<tr>
<td>333</td>
<td>14</td>
<td>15.4 ± 0.1 Å</td>
<td>19.8 ± 0.6 Å</td>
<td>4.4 ± 0.6 Å</td>
</tr>
<tr>
<td>328</td>
<td>18</td>
<td>19.9 ± 0.1 Å</td>
<td>23.7 ± 0.4 Å</td>
<td>3.8 ± 0.4 Å</td>
</tr>
<tr>
<td>374</td>
<td>23</td>
<td>27.3 ± 0.1 Å</td>
<td>29.0 ± 0.2 Å</td>
<td>1.7 ± 0.2 Å</td>
</tr>
</tbody>
</table>
Table 3.2. The barrier thickness, tunneling current density and applied voltage comparison of Au/SAM/Al₂O₃/Au structure with similar noble metal tunnel structures.

<table>
<thead>
<tr>
<th>Sample</th>
<th>Structure</th>
<th>Barrier thickness (Å)</th>
<th>Tunneling current density (A/cm²)</th>
<th>Applied voltage (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>No.333</td>
<td>Au/SAM/Al₂O₃/Au</td>
<td>19.8 ± 0.6</td>
<td>0.20 ~ 0.75</td>
<td>0.5</td>
</tr>
<tr>
<td>Ref. [100]</td>
<td>NiFe/Al/AlOₓ/NiFe</td>
<td>20.0</td>
<td>10 ~ 20</td>
<td>0.5</td>
</tr>
<tr>
<td>No.328</td>
<td>Au/SAM/Al₂O₃/Au</td>
<td>23.7 ± 0.4</td>
<td>(3.4 ~ 8.6)×10⁻³</td>
<td>0.5</td>
</tr>
<tr>
<td>No.374</td>
<td>Au/SAM/Al₂O₃/Au</td>
<td>29.0 ± 0.2</td>
<td>(1.4 ~ 2.3)×10⁻⁵</td>
<td>0.5</td>
</tr>
<tr>
<td>Ref. [110]</td>
<td>Pt/Al/AlOₓ/Pt</td>
<td>&gt; 30.0</td>
<td>~ 6×10⁻³</td>
<td>0.5</td>
</tr>
<tr>
<td>Ref. [111]</td>
<td>Au/Si₃N₄/SiO₂/Au</td>
<td>35.0</td>
<td>~ 6×10⁻³</td>
<td>0.3</td>
</tr>
</tbody>
</table>
Figure 3.4. AFM images of (a) Al 5 nm/Au 20 nm, (b) Al 5 nm/Au 20 nm/SAM, (c) Al 5 nm/Au 20 nm/SAM/Al₂O₃ 2 nm and (d) Al 5 nm/Au 20 nm/Al₂O₃ 2 nm structures. Rms roughness of (a), (b), (c) and (d) are about 0.5 nm, 0.6 nm, 0.6 nm and 0.9 nm, respectively. All samples use thermally grown SiO₂ on Si wafer as the
Figure 3.5. Schematic side views of ALD Al₂O₃ layer on Au thin film surface (a) with and (b) without HSCH₂CH₂OH SAM interlayer.
Chapter 4

Molecular attachment on nanogap electrode by Au/Al₂O₃/Au multilayer structure

4.1 Introduction

In Chapter 3, we introduced Au/SAM/Al₂O₃/Au multilayer structures by growing a nano-scale high quality Al₂O₃ insulating layer on monolayer surface chemistry (119). The gap between Au electrodes can be as small as 2 nm and is ideal to study molecular conduction mechanisms with the well controlled Au-thiol surface.

In this chapter, two different molecules were applied to bridge the nano-gap gold electrodes. One molecule is Molecule II already introduced in Section 2.5. Another molecule is a smaller but simpler single metal complex (Molecule III, see Figure 4.1) composed of two 1-Octanethiol, 8-([2,2':6',2''-terpyridin]-4'-ylthio) molecules and a metal core of Fe²⁺. Control experiments were executed to prove the molecular attachment on both electrodes. A low temperature conductivity study shows the molecular current temperature independent confirming a direct tunneling mechanism.

4.2 Experimental details

4.2.1 Molecular attachment
To attach Molecule II to Au electrodes, the nano-gap electrodes were immersed in a 2mM solution of OMC in a dichloromethane (CH$_2$Cl$_2$) solvent for 2 min. Then the sample was sequentially cleaned with isopropyl alcohol (IPA), deionized (DI) water, and nitrogen drying.

Two steps were executed to attach Molecule III to Au electrodes, as shown in Figure 4.2. Nano-gap electrodes were first immersed in a 2mM solution of 1-Octanethiol, 8-[(2,2':6',2''-terpyridin]-4'-ylthio) in an IPA solvent for 2 hours. After cleaning by IPA, DI water, and nitrogen drying, the nano-gap electrodes were immersed in a 2mM FeCl$_2$ solution for 2 hours to form molecule complexes. Finally, the electrodes were sequentially cleaned with IPA, DI water, and nitrogen drying.

**4.2.2 Control experiments**

To verify that attached molecules are bridging the top and bottom electrodes, control experiments were executed to reversibly detach and re-attach the molecule across the electrode. This would show that the observed current increase is not due to an artifact of insulator breakdown. After molecular attachment described in last section, the sample was first immersed in a 10 mM solution of β-mercaptoethanol in an IPA solvent for 12 h. After cleaning by IPA, DI water, and nitrogen drying, the sample was immersed in a 2 mM solution of Molecule II/III for another 12h. Then, the sample was sequentially cleaned with IPA), DI water, and nitrogen drying.

$I$-$V$ curves of the Al/Au/SAM/Al$_2$O$_3$/Au structure with/without molecular attachment were performed at room temperature by a Keithley 2430 1KW Pulse Sourcemeter, a
Keithley 6430 Sub-femtoamp Remote Sourcemeter, and an MM Micromanipulator probe station. Low temperature studies were performed at an MMR LTMP-4 cold probe station with a K-20 programmable temperature controller. The temperature cooling rate is ~10 K/min.

4.3 Results and discussions

Transport studies of the Si/SiO$_2$ 100 nm/Al 5 nm/Au 20 nm/SAM 0.4 nm/ Al$_2$O$_3$ 1.7 nm/Au 20 nm structure (sample No.405) before and after Molecule II attachment are shown in Figure 4.3a. The $I$-$V$ curve of the bare junction shows typical tunnel junction properties. The $I$-$V$ curve of the nano-gap electrode bridged by molecules is close to a linear line. The current at 0.3 V before and after molecule attachment is $1.2 \times 10^{-8}$ A and $1.7 \times 10^{-7}$ A, respectively. The current enhancement after molecule II attachment indicates current passing through molecule II dominating the total sample current. If the sample is short from junction failure, the current level will reach $10^{-3}$ A level at 0.3 V.

Molecular current is defined as the total sample current minus the bare junction current at any bias. The edge length of the top electrode at the junction area is ~10 μm (see Figure 3.1b) and the scale of Molecule II is considered around 2 nm. If all molecules are closely packed with a spacing length of 1 nm, an array of approximately 20,000 molecules covalently attach along the two sides of the top electrode. The average current per molecule was estimated to be $8.0 \times 10^{-12}$ A at 0.3 V. Therefore, the average molecular resistance is about $3.8 \times 10^{10}$ Ω, compared to the HS(CH$_2$)$_{10}$SH resistance of about $10^9$ Ω$^{(62, 120)}$ and the HS-(CH$_2$)$_9$-CH$_3$ of about $10^{12}$ Ω$^{(62, 121)}$ by the Probe Scanning Microscopy (PSM) using an applied voltage from -0.3 V to 0.3 V. The Molecule I resistance,
measured by a similar NiFe/Al₂O₃/Ni tunnel junction structure, is ~ 4.5×10⁹ Ω (100). All these comparisons are listed in Table 4.1.

Molecule III has similar I-V characteristics as Molecule II, as shown in Figure 4.3. The average current per molecule was estimated to be 8.5×10⁻¹² A at 0.3 V and the average molecular resistance is about 3.5×10¹⁰, close to the calculated data of Molecule II.

The Au-S bond is reversible and it is possible to remove the thiol linkage by mass action/exchange in a thiol-alkane solution. Figure 4.4 shows the control experiment results. The electrode current increased after Molecule II first attachment and returned to the bare junction level after the thiol group exchange of the alkyl tether of Molecule II with the thiol group of β-mercaptoethanol by exposure to a 10 mM solution of β-mercaptoethanol in an IPA solvent for 12 h. The β-mercaptoethanol molecules replaced Molecule II and could not bridge the top and bottom electrodes. This is the reason why the current returned to the original bare electrode current level after the Au-S exchange reaction. The electrode current increased when the sample was immersed in a 2 mM solution of Molecule II for a second time. The observed molecular current was 4.8×10⁻⁹ A at 0.5 V while the molecular current after the first Molecular attachment was 2.2×10⁻⁸ A at 0.5 V, indicating a partial exchange of β-mercaptoethanol (~ 22%) by Molecule II. These control experiments confirm that the current enhancement is due to the molecular attachment across the dielectric, not due to an artifact of the breakdown of the dielectric layer within the tunnel junctions.

Figure 4.5a shows the I-V characteristics of Molecules (II) attached at the edge of the Au/SAM/Al₂O₃/Au structure at 293 K and 80 K; and Figure 4.5b shows the current
passing through the same molecules with an applied voltage of 0.5 V at different temperatures. The constant current over the large temperature range in Figure 4.5 indicates the molecular current is only generated by a tunneling mechanism without any thermal activation. The bare tunnel junction current was also measured at different temperatures and the observed $I$-$V$ curves are temperature independent, consistent with the tunneling process. This result indicates the SAM/Al$_2$O$_3$ insulating layer as a high quality film structure without any hopping mechanism defects. The sample was irradiated with light (15mW/cm$^2$) and no increase current was detected, as shown in Figure 4.6. This result also indicates the molecular current is only through direct tunneling. In particular no photo-exited states at or below the Fermi level within the molecule increase current, indicating that empty electron states are available as conduction channels. Also the photo excitation of carriers does not overcome small defect barriers in the oxide insulator barrier or in contacts. In the case of the prior report$^{(100)}$ and thesis, Molecule I on NiFe leads showed photo current increase and a crude measurement of activation energy of 0.3V, which is likely related to transport through oxide tunnel barrier defects. The work function of Ni is 5.01 eV and is very similar to Au at 5.1eV. Since Au has a higher work function, any barrier to electron transport to the metal center (i.e. occupied states in the molecule at the Fermi energy), would be higher in the Au case compared to Ni (by 0.1eV). However no barrier was experimentally seen in the Au case, therefore no barrier is expected in the Ni case.

Simmons model is used to calculate the barrier thickness (nm) and barrier height (eV) by fitting the observed $I$-$V$ curves$^{(66)}$. The fitting curves are shown in Figure 4.7 a&b. The tunneling area of the bare junction is $\sim 75 \mu m^2$. We assume Molecule II as a cubic of $a =$
1 nm. Therefore, the tunneling area of all attached molecules is \(1 \text{ nm} \times 10 \ \mu\text{m} \times 2 = 0.02 \ \mu\text{m}^2\). The simulation results show a barrier thickness of 21.7 Å and a barrier height of 1.2 eV for the bare junction without molecule current path. After the attachment of Molecule II, a barrier thickness of 11.6 Å and a barrier height of 1.4 eV is seen for the device. The simulated barrier thickness of Molecule II is consistent with tunneling through the 10-carbon-alkane-tether length in Molecule II, which is around 12 Å to the metal center instead of across the entire 30 Å molecule.

Effective barrier thicknesses for the molecular transport component of electrodes functionalized by Molecule II were calculated for a series of Au/SAM/Al₂O₃/Au samples. The barrier height of bare tunnel junctions and Molecule II are 1.2 eV and 1.4 eV, respectively. All Au tunnel junctions in this chapter were fabricated with 15 Al₂O₃ ALD growth cycles with the resulting thickness of the Al₂O₃ layer of \(\sim 16.5 \ \text{Å}\). The SAM layer thickness is \(\sim 4 \ \text{Å}\), calculated in Chapter 3. Therefore, the total thickness of the SAM/Al₂O₃ dielectric stack is \(\sim 20.5 \ \text{Å}\), consistent with the barrier thickness of bare tunnel junctions of \((21.4 \pm 0.8) \ \text{Å}\) in Figure 4.7. The barrier thickness of Molecule II is \((12.3 \pm 1.0) \ \text{Å}\), consistent with the expected length of the 10-carbon-alkane-tether length of 12 Å.

Figure 4.9 shows the working mechanism of this molecular device. There are two tunneling paths. The first tunneling path is from the top electrode to the bottom electrode directly. This tunneling length is \(\sim 21.4 \ \text{Å}\). The second tunneling path is through Molecule II composed of four 10 carbon alkane tethers and one metal cage. The metal cage can be considered as a metal island between the top and bottom electrodes. Therefore, current can tunnel from the top electrode to the metal cage first and tunnel again from this metal cage to the bottom electrode. Although the barrier height of the 10
carbon alkane tether (1.4 eV) is a little higher than that of the SAM/Al₂O₃ insulating structure (1.2 eV), the length of the 10 carbon alkane tether (~ 12.3 Å) is much smaller than that of the thickness of the SAM/Al₂O₃ insulating structure (~ 21.4 Å) and within the uncertainty of tunnel barrier thickness with the two adjustable parameters. This difference leads to a higher tunneling current density of 8.0×10² A/cm² passing through Molecule II compared to that of 1.6×10⁻² A/cm² passing through the SAM/Al₂O₃ insulating stack at 0.3 V.

Since the tunneling current passing through the tether of Molecule II is coherent, the tunneling decay parameter $\beta$, introduced in Section 1.6.1.2, can be calculated to describe the 10 carbon alkane tether. The calculated $\beta$ of Molecule II is 0.96 Å⁻¹ by equation (1.24). This result is consistent with the alkane tether $\beta$ value of 0.6 ~ 1.0 Å⁻¹ (62, 63). Table 4.1 shows the comparison of calculated values of barrier thickness, barrier height, $\beta$, $T_{mol}$ and resistance of Molecule II & III with similar noble metal contacts. The resistance of Molecule II is larger than the AFM measurement of decanedithiol (120). This is due to a combination of a two-step tunneling of electrons through Molecule II and the additional resistance of the perazylborate ligand. And the resistance of Molecule II is smaller than the AFM measurement of decanethiol in Ref. (121) This is due to the Au-CH₃ contact, not the Au-S contact, between the molecule and the AFM tip. This Au-CH₃ contact increases the total molecular resistance.

Molecule I & II have a similar structure. The only difference is the thiol acetyl group in Molecule I replaced by the hydrogen (thiol) atom in Molecule II. This allows the direct reaction with Au for Molecule II instead of requiring electrochemical activation of Molecule I. With the NiFe electrodes (100), the electrochemical activation process
corroded electrodes and was highly irreproducible due to solvent evaporation and HCl formation in the dichloromethane solvent. Thus, we chose to focus on Molecule II. After molecular attachment on metal electrodes, both molecules I & II are identical and should show similar current transport properties through metal-S bonds. The prior study with Molecule I on Ni electrodes with liftoff process showed a barrier height of $\sim 0.74$ eV \(^{(100)}\) that is much smaller than Molecule II on Au electrodes in this study with a barrier height of 1.4 eV. Following the Equation (1.24), the calculated $\beta$ is $0.74 \, \text{Å}^{-1}$ for Molecule I on these Au contacts. The prior work on Ni contacts with poor background tunnel current showed the $\beta$ value of $0.88 \, \text{Å}^{-1}$\(^{(100)}\). The resistance of Molecule I is much smaller than that of Molecule II mainly because Molecule I has a much smaller barrier height than Molecule II. A thermal activation energy of $\sim 0.30$ eV was detected for Molecule I while the I-V characteristics of Molecule II is constant over a larger range at different temperatures. This suggests a defect conduction mechanism through a poorer quality tunnel barrier rather than through molecular conduction. Considering the poor repeatability of experiments in Ref.\(^{(100)}\), attempted by myself under the prior student’s direct supervision and the observation of oxide layers on Ni electrodes (Ch 2), the data of Molecule I is not comparable in Table 4.1.

Molecule II attachment on the Au with a small barrier height was seen in only a few devices as shown in Figure 4.10. The low current level and curvature are typical for a large tunnel barrier length. The Simmons simulation shows a barrier thickness of 19.9 Å and a barrier height of 0.6 eV for these attached Molecule II arrays. This is very different than the prior work with Molecule I where both low energy ($\sim 0.74$ eV) and short (13 Å) barrier were inferred from Simmons model. In this case, the barrier thickness is close to
the thickness of the insulator layer (22 Å) and difficult to analyze with respect to defects in the electrode structure or decomposition product without metal bridging center.

4.4 Conclusions

Different molecules were attached on the exposed edges of Au/SAM/Al₂O₃/Au tunnel junctions to bridge the top and bottom electrodes. The repeatable Au-S exchange control experiments prove the dominant current passing through molecules. The calculated barrier thickness of ~ 12.3 Å by Simmons model, consistent with the 10-carbon alkane tether length of ~ 12 Å, demonstrates the molecular current tunneling through the metal center of studied molecules. Low temperature and photo current studies show a direct tunneling through the organic tethers to available states at the metal center.
Figure 4.1. Schematic drawing of Molecule III
Figure 4.2. Two step attachment of Molecule III to bridge Au electrodes.
Figure 4.3. $I-V$ characteristics of Au/SAM/Al$_2$O$_3$/Au tunnel junctions before and after (a) Molecule II and (b) Molecule III attachment.
Figure 4.4. $I$-$V$ characteristics of Au/SAM/Al$_2$O$_3$/Au tunnel junctions with the Molecule II attachment and the thiol-exchange reaction in a 10 mM β-mercaptoethanol solution.
Figure 4.5. (a) $I$-$V$ characteristics of Molecules (II) attached at the edge of the Au/SAM/Al$_2$O$_3$/Au structure at 293 K and 80 K; (b) Currents passing through Molecule (II) attached along the edge of the Au/SAM/Al$_2$O$_3$/Au structure with an applied voltage of 0.5 V at different temperatures.
Figure 4.6. $I$-$V$ characteristics of Molecules (II) attached at the edge of the Au/SAM/Al$_2$O$_3$/Au structure in dark and light. The incident light density is 15 mW/cm$^2$. 
Figure 4.7. $I$-$V$ characteristics (■) and Simmons simulation (▬) of (a) a bare Au/SAM/Al$_2$O$_3$/Au tunnel junction and (b) Molecule II current derived from the difference between two curves in Fig. 4.3.
Figure 4.8. Barrier thickness of Au/SAM/Al₂O₃/Au tunnel junctions bridged by Molecule II. The barrier height of bare tunnel junctions and Molecule II are 1.2 eV and 1.4 eV, respectively.
Figure 4.9. Schematic drawing of the current tunneling in a molecular device and the idealized band diagram. $E_f$ is the Fermi energy level of Au electrodes, $\sim 1.2$ eV and $\sim 1.4$ ev are the barrier height of the bare tunnel junction and Molecule II, respectively.
Table 4.1. The barrier thickness, tunneling current density and applied voltage comparison of Au/SAM/Al₂O₃/Au structure with similar noble metal contacts.

<table>
<thead>
<tr>
<th>Molecule</th>
<th>Carbon number</th>
<th>Technique</th>
<th>Barrier thickness (Å)</th>
<th>Barrier height (eV)</th>
<th>$\beta$ (Å⁻¹)</th>
<th>$T_{mol}$</th>
<th>Resistance per molecule (Ω)</th>
</tr>
</thead>
<tbody>
<tr>
<td>II</td>
<td>10</td>
<td>Au tunnel junction</td>
<td>12.3 ± 1.0</td>
<td>1.4</td>
<td>0.96</td>
<td>~ 7.4 × 10⁶</td>
<td>~ 1.0 × 10¹¹</td>
</tr>
<tr>
<td>I¹(100)</td>
<td>10</td>
<td>NiFe/Ni tunnel junction</td>
<td>13.0 ± 2.9</td>
<td>~ 0.74</td>
<td>0.74¹</td>
<td>~ 6.6 × 10⁵</td>
<td>1 × 10⁸ ~ 3 × 10¹⁰</td>
</tr>
<tr>
<td>HS(CH₂)₉SH¹(120)</td>
<td>10</td>
<td>AFM²</td>
<td>N/A</td>
<td>N/A</td>
<td>0.91</td>
<td>~ 1.1 × 10⁴</td>
<td>~ 6.3 × 10⁸</td>
</tr>
<tr>
<td>HS(CH₂)₉CH₃¹(121)</td>
<td>10</td>
<td>AFM²</td>
<td>N/A</td>
<td>N/A</td>
<td>0.79</td>
<td>N/A</td>
<td>~ 2.0 × 10¹²</td>
</tr>
<tr>
<td>III</td>
<td>8</td>
<td>Au tunnel junction</td>
<td>11.2</td>
<td>1.4</td>
<td>0.96</td>
<td>2.1 × 10⁴</td>
<td>~ 3.5 × 10¹⁰</td>
</tr>
<tr>
<td>HS(CH₂)₉SH¹(120)</td>
<td>8</td>
<td>AFM²</td>
<td>N/A</td>
<td>N/A</td>
<td>0.91</td>
<td>~ 2.5 × 10⁷</td>
<td>~ 5.1 × 10⁷</td>
</tr>
<tr>
<td>HS(CH₂)₉CH₃¹(121)</td>
<td>8</td>
<td>AFM²</td>
<td>N/A</td>
<td>N/A</td>
<td>0.79</td>
<td>N/A</td>
<td>~ 2.0 × 10¹¹</td>
</tr>
</tbody>
</table>

Note: 1. The $\beta$ value of Molecule II in Ref.(100) is 0.88 Å⁻¹.

2. All AFM techniques in this table used a gold layer to cover the cantilever tips and a gold substrate to attach molecules.
Figure 4.10. $I$-$V$ characteristics of Molecules (II) attached at the edge of the Au/SAM/Al$_2$O$_3$/Au structure with a low barrier height of 0.6 eV.
Chapter 5

Fabrication and study of organic photodetectors by Au/Al$_2$O$_3$/Au multilayer structures

5.1 Introduction

In Chapter 3, we introduced Au/SAM/Al$_2$O$_3$/Au multilayer structures by growing a nano-scale high quality Al$_2$O$_3$ insulating layer on monolayer surface chemistry where the gap between Au electrodes can be as small as 2 nm $^{122}$. This nano-gap electrode is a good substrate for molecular study. Another application of this nano-gap electrode is the photovoltaic study of organic semiconductors in a nanoscale. This idea can be realized by depositing organic semiconductors between the nano-gap electrodes.

In this chapter, we used sputtering, atomic layer deposition (ALD), and Ar milling to fabricate the exposed edge of Au/Al$_2$O$_3$/Au multilayer structure to minimize the contact resistance between organic semiconductor and metal electrodes. The well characterized Copper (II) phthalocyanine (CuPc) was chosen as the organic semiconductor because of its stability and facile deposition by thermal evaporation $^{88, 123}$. Large photocurrent enhancement over 50 times that of bulk CuPc film was observed due to the gap between Au electrodes approaching 10 nm. Schottcky barrier contact resistance was found to be the primary limiter of charge injection into the organic film.
5.2 Experimental details

The structure of CuPc film photodiode on the exposed edge of Al/Au/Al₂O₃/Au/Ti multilayer is schematically shown in Fig. 5.1. Figure 5.2 shows the fabrication flow. Prior to sample preparation, the SiO₂ wafer (Silicon Quest International, Inc.) with a 1000 Å thick SiO₂ layer grown thermally on Si substrate was sequentially cleaned with acetone, isopropyl alcohol (IPA), deionized (DI) water and dried in a nitrogen stream. The bottom electrode was lithographically patterned to a size of 2 mm × 10 mm and 50 Å of Al and 500 Å of Au were thermally evaporated using a Cressington 308R Coating System. The Al₂O₃ insulating layer was fabricated in three steps. First, 10 Å of Al was sputtered in an AJA International high vacuum sputtering system with a base pressure of 8.0×10⁻⁸ torr and oxidized in an O₂ flow at 60 mTorr for 2 min to form an Al₂O₃ seed layer with a thickness of ~ 12 Å. Then atomic layer deposition of Al₂O₃ (38, 88, 188, 488, and 988 Å for sample A (No.347), B (No.311), C (No.339), D (No.359), and E (No.357), respectively) was carried out in a Cambridge Nanotech Savannah 100 system. In order to protect Al₂O₃ film from being etched by the alkaline photoresist developer, 200 Å of Au was sputtered on the Al₂O₃ insulating layer. The top Ti layer (500 Å for sample A, B & C and 2000 Å for sample D & E) was lithographically patterned into microwires (8 μm × 1000 μm) by e-beam evaporation in a Torr International EB4P series system. Ar ion milling at the Plasmalab 80plus system was carried out to expose the edge of Au/Al₂O₃/Au structure by etching 200 Å Au protection layer and the whole Al₂O₃ insulating layer. The top Ti pattern was also partially etched and the remaining Ti layer was then plasma oxidized with 60 mTorr of 1:1 Ar/O₂ gas mixture to form an insulating TiO₂ thin film on the surface. Ti/TiO₂ on probe station contact pad areas was removed by
0.05 M HCl solution to expose Au surface for probe attachment. Finally, CuPc (Aldrich Chemical, 99% purity) was thermally deposited on the exposed Au/Al₂O₃/Au/Ti/TiO₂ structure area using a shadow mask.

All I-V characters were performed at room temperature by Keithley 2430 1KW Pulse Sourcemeter or 6430 Sub-femtoamp Remote Sourcemeter at the MM Micromanipulator probe station. AFM measurements were made by a tapping mode AFM (Digital Instruments Multimode) and SEM images were recorded using a Hitachi S4300 system. The Al₂O₃ film thickness was confirmed by Spectroscopic Ellipsometers (M-2000V, J.A.Woollam Co. Inc.). The light source for the photoconductivity experiment was manufactured by Micro-Lite FL3000D. The maximum irradiated power reaching samples was 15.8 mW/cm².

5.3 Results and discussion

Figure 5.3(a) shows the optical microscope image of sample A (5 nm Al/50 nm Au/5nm Al₂O₃/20 nm Au/Ti/TiO₂) bare tunnel junction structure without CuPc deposition. Each top electrode has a length of 1000 μm and a width of 8 μm. The SEM image of the circled area in Figure 5.3(a) is shown in Figure 5.3(b). The grains of the bottom Au electrode are clearly observed and the top electrode is covered with a TiO₂ layer. A step height of 60 nm for the top electrode is obtained from the 3D AFM image in Figure 5.3(c). Thus the thickness of Ti/TiO₂ structure is about 30 nm after over etching the Al₂O₃ insulating layer that is over the bottom electrode. The purpose of the top Ti/TiO₂ layer is to block current flow from the relatively large upper surface of the top Au
electrode to the bottom Au electrode. Thus, the current path between Au electrodes via CuPc film can be controlled at the nano-scale film thickness at the pattern edge, as the arrow shown in Figure 5.1. The leakage current of these tunnel junctions through the Al2O3 layer in the planar area between top and bottom electrodes is very low (~ $10^{-12}$ A at 0.5 V) for sample A and even lower for other samples having larger Al2O3 thicknesses.

Figure 5.4(a) shows both dark and photo current versus applied voltage of sample A deposited with a 70 nm CuPc film. The dark current, $3.0 \times 10^{-9}$ A at 0.5 V, is 3 orders of magnitude larger than the leakage current of bare tunnel junctions, confirming that most of the current flows through the CuPc film. The net photocurrent-voltage characteristics of sample A (5nm gap width), calculated by subtracting the dark current from photocurrent in Figure 5.4(a), is illustrated in Figure 5.4(b). The net photocurrent increases with an increasing incident light intensity. A linear plot (linear regression of ~1.2) of the logarithm of the photocurrent (measured at 0.5 V) versus the logarithm of light intensity is shown in Figure 5.4(c). It is very clear that there is a power law dependence of the photocurrent on the incident light intensity. The corresponding exponent value is about 0.53, which is consistent with reports (0.5 ~ 1.0) in the literature.

The relationship between net photocurrent and the electrode’s gap distance (also the thickness of Al2O3 layer) is demonstrated in Figure 5.5. All samples were measured with an incident light intensity of 15.8 mW/cm² and an applied voltage of 0.5 V. Photocurrent increases when the gap distance decreases from 100 nm to 20 nm. A large photocurrent enhancement is observed when the gap scale is approaching 10 nm. The average photocurrent of $6.2 \times 10^{-9}$ A with a 10 nm gap is almost over 10 times larger than the
5.2×10^{-10} \ \text{A} \text{ of a 20 nm gap, and over 50 times larger than the 1.1×10^{-10} \ \text{A} \text{ of a 100 nm gap. This enhancement shows the important role of the gap distance to the generated photocurrent.}

The CuPc carrier recombination length can be calculated from observed photocurrents using a simple model, in which the top and bottom Au electrodes are considered as parallel plates, drawn schematically in Figure 5.6(a). The width of plates is equal to the thickness of the top Au electrode (W). The gap between parallel plates (D) is a combination of Al₂O₃ layer and half of the top Au layer (10 nm). The current flux is from the top to bottom through CuPc film (the dark region in Figure 5.6(a)) when a higher electric potential is applied to the top Au electrode. For a semiconductor film, the steady-state photoconductivity is given by

$$
\Delta \sigma = \frac{e \eta \lambda \tau \mu}{hcD}
$$

(5.1)

where e is the electron charge 1.6×10^{-19} \ \text{C}, \eta \text{ is the efficiency of photons converting to free electron-hole pairs and as assumed to be 0.5 in this work, } I \text{ is the light intensity 15.8 mW/cm}^2, \lambda \text{ is wavelength of the incident light (600 nm is used here), } \tau \text{ is the recombination lifetime of the photogenerated carriers, } \mu \text{ is carrier mobility, } h \text{ is Planck’s constant, } c \text{ is velocity of light, } D \text{ is the thickness of the semiconductor film, } \Delta \sigma \text{ is the steady-state photoconductivity which can be calculated from the observed photocurrents in Figure 4.4. When a voltage } U \text{ (0.5 V) is applied on the parallel plate model in Figure 5.6(a), the carrier recombination length is given by}
where $E$ is the electric field intensity of the dark region in Figure 5.6(a). So

$$L_D = \mu E \tau = \frac{U \mu \tau}{D}$$  \hspace{1cm} (5.2)

Table 5.1 shows the calculated carrier recombination length with different gap distances and applied voltages. The calculated carrier recombination lengths with a gap distance of 20 nm, 50 nm and 100 nm, respectively, are smaller than the corresponding electrode gap distance. Often the electrons recombine with the holes rather than reach the Au electrodes. The calculated effective recombination length of 5nm gap and 10 nm gap are much larger than the physical length because equation (5.1) is for semiconductor bulk films, whose thickness is larger than the carrier recombination length of this semiconductor material. In sample A & B, the carrier travel distance is within 10 nm so that the majority electrons and holes can reach electrodes to generate photocurrent resulting in longer effective recombination lengths. Sample B has a longer path length and subsequently larger volume for electron/hole pair generation from the light, which leads to a larger photocurrent of sample B than that of sample A. In equation (5.3), the applied voltage $U$ is directly proportional to $L_D$. When the applied voltage between two electrodes is increased, a larger effective carrier diffusion length is generated.

Four-point probe and two-point probe methods were used to measure the contact resistance between Au electrodes and CuPc film and bulk conductivity. The top electrodes in Figure 5.3(a) were used as probes with a distance of 150 μm between
adjacent electrodes. A contact resistance of $3 \times 10^7 \Omega$ and a bulk CuPc resistance of $3 \times 10^9 \Omega$ are obtained. Our observed CuPc conductivity is $6 \times 10^{-9} \text{ cm}^{-1}$, that is within the experimentally observed range of $10^{-10} \sim 10^{-8} \text{ cm}^{-1}$ from literature (124-126). When the gap scale between electrodes approaches 5 nm, the CuPc resistance should decrease to $3 \times 10^9 \Omega \times (5 \text{ nm}/150 \mu \text{m}) = 1 \times 10^5 \Omega$ while the contact resistance still keeps a level of $10^7 \Omega$. This illustrates that the contact resistance is dominant in all I-V measurements.

It is interesting that both dark and light I-V curves of all samples show diode characteristics. In Figure 5.7(a), with sample A in the dark, a large current of 3 nA was detected when the top electrode was applied with + 0.5 V while a small current of 0.3 nA was detected when the bottom electrode was applied with the same potential. However, sample A should have a symmetrical I-V curve because of the symmetric contacts of Au/CuPc/Au. The only explanation is that Schottky junctions are formed between Au and CuPc for samples in this work while Ohmic contacts are generally assumed for the bulk measurements since with longer path lengths the bulk organic resistance dominates the measurement. The energy level diagram, for all samples, is drawn in Figure 5.8 to explain the observed diode behavior and contact resistance. We assume that the Schottky barrier height is $a$ eV and the band gap between CuPc HOMO and Fermi level is $(a-b)$ eV without any applied bias ($V_{DS} = 0$ V), as illustrated in Figure 5.8(a). When -0.5 V is applied on the bottom electrode, a potential drop between the top electrode and CuPc film ($V_1$) and a potential drop between the bottom electrode and CuPc film ($V_2$) are generated. $V_1$ has a larger value than $V_2$ because the contact area of the top electrode with CuPc film is smaller than that of the bottom electrode, which leads to a larger contact resistance of the top electrode than that of the bottom electrode (see Figure 5.1). As mentioned above,
the contact resistance between Au electrodes and CuPc film is far larger than the CuPc film resistance. So \( V_1 + V_2 \approx 0.5 \, V \) and a horizontal energy level of the CuPc film is drawn in Figure 5.8(b) & (c). It is obvious that holes need to overcome one large barrier \( a \, eV \) and one small barrier \( (b - V_2) \, eV \) in Figure 5.8(b) and only need to overcome one barrier \( a \, eV \) in Figure 5.8(c).

5.4 Conclusions

CuPc thin films were successfully deposited between electrodes with a gap distance smaller than the CuPc carrier recombination length. The 10 nm-gap photocurrent of CuPc film is over 10 times larger than 20 nm-gap photocurrent and over 50 times larger than 100 nm-gap photocurrent. This large photocurrent enhancement is the result of the nano-gap’s size being shorter than the CuPc carrier recombination length thereby minimizing the recombination of electron-hole pairs. The large Schottky barrier contact resistance between the small area top Au electrode and the CuPc film is responsible for the diode \( I-V \) characteristics of devices in this work and is the primary limiter of efficiency.
Figure 5.1. Schematic side view of the Al/Au/5 nm Al₂O₃/Au/Ti/TiO₂/CuPc device used in this study.
Figure 5.2. Schematic drawing of a photodetector with an Al/Au/Al₂O₃/Au/Ti/TiO₂/CuPc structure.
Figure 5.3. (a) optical microscope image of the bare tunnel junction with Al/Au/5 nm Al₂O₃/Au/Ti/TiO₂ structure and (b) SEM and (c) AFM images of the circle area in (a). The scale bar in (a) is 200 μm and z scale bar in (c) is 100 nm in the vertical direction. The insert image in (c) is the profile analysis of the top electrode.
Figure 5.4. (a) Total photocurrent-voltage and (b) net photocurrent-voltage characteristics of Al/Au/5 nm Al₂O₃/Au/Ti/TiO₂/CuPc devices measured at room temperature with different light intensity and (c) variation of photocurrent with light intensity (applied voltage 0.5 V).
Figure 5.5. Net photocurrent *versus* the gap distance between Au electrodes. The incident light intensity is 15.8 mW/cm$^2$ and applied voltage is 0.5 V.
Table 5.1. The carrier recombination length (nm) with different gap distances derived from the real photocurrent in Fig. 5.4.

<table>
<thead>
<tr>
<th>Applied voltage (v)</th>
<th>5</th>
<th>10</th>
<th>20</th>
<th>50</th>
<th>100</th>
</tr>
</thead>
<tbody>
<tr>
<td>0.2</td>
<td>11 ± 4</td>
<td>25 ± 9</td>
<td>2.3 ± 0.4</td>
<td>2.5 ± 0.4</td>
<td>2.9 ± 0.8</td>
</tr>
<tr>
<td>0.4</td>
<td>32 ± 11</td>
<td>71 ± 25</td>
<td>7.4 ± 1.6</td>
<td>7.9 ± 1.4</td>
<td>7.5 ± 2.2</td>
</tr>
<tr>
<td>0.5</td>
<td>49 ± 17</td>
<td>94 ± 38</td>
<td>13 ± 3</td>
<td>11 ± 2</td>
<td>11 ± 3</td>
</tr>
</tbody>
</table>
Figure 5.6. Schematic drawing of the model used to calculate CuPc carrier recombination length.
Figure 5.7. (a) Dark and (b) light current-voltage characteristics of Al/Au/5 nm Al₂O₃/Au/Ti/TiO₂/70 nm CuPc device measured by (●) top electrode and (△) bottom electrode connecting to the power source. The incident light intensity is 15.8 mW/cm².
Figure 5.8. Energy level diagram for the Al/Au/5 nm Al₂O₃/Au/Ti/TiO₂/70 nm CuPc device: (a) zero bias; (b) $V_{DS} = -0.5$ V and (c) $V_{DS} = 0.5$ V with power source connecting to the bottom electrode. $V_1$ & $V_2$ are the voltage drops between top & bottom electrodes, respectively; $V_1 + V_2 \approx 0.5$ V and $V_1 > V_2$. 
Chapter 6

Growth study of lateral ZnO nanowire growth from the exposed edge of Si/Al$_2$O$_3$/Si trilayer structures

6.1 Introduction

The previously discussed multilayer electrodes have approximately 10,000 molecules spanning nm-scale gaps over the 10 linear microns of junction length. If we can couple an orthogonal pattern of nm-scale dimension it would be possible to develop electrodes that isolate single molecules. A promising approach is to have nanowires projecting over the edge of multilayer electrodes to cast nm-scale shadows in a line of site deposition of an insulator which would leave only a few nm$^2$ area for molecular attachment on the electrode, isolating single molecules. ZnO nanowires are promising due to their ease of growth and controlled nucleation sites that can be incorporated into the electrode geometries. Our group has generated nm-scale gaps in line-of-site depositions successfully by carbon nanotubes (CNTs) that showed reduction in critical dimension by line incident angle and nanowire height$^{(101, 127, 128)}$. However, this approach requires controlled lateral growth from defined locations and control of nanotube/wire diameter. To control the diameter of CNTs, one can take advantage of the angstrom scale precision of film thickness at a thin-film multilayer pattern edge to control the width of a catalyst line. This thickness was used to determine the diameter of CNTs growing from pattern edge. However, these CNTs were not rigid or straight enough to be used as
shadow masks. ZnO NWs are rigid and straight and are well suited for shadow lithography applications.

Among 1-D nanostructures, ZnO nanowires (NWs) have become an actively researched area because of their beneficial semi-conductive properties (a wide bandgap of 3.37 eV and large exciton binding energy of 60 mV), easy synthesis (129, 130), photo catalytic activity (131, 132) and potential for integration into the sensor platform (133, 134). Grown with the vapor-liquid-solid (VLS) mechanism, the position and diameter of ZnO NWs are well controlled by the location and size of metal catalysts (especially Au) (131, 135-140). Recently, catalyst-free ZnO NWs have been developed (141-146) to simplify the fabrication process and eliminate potential contamination in semiconductor devices. ZnO islands or films formed first by physical deposition or chemical synthesis provide the nucleation area for the growth of 1-D nanostructures.

The control of location, diameter and length of NWs are critical for nanodevice fabrication. Several reports demonstrated the vertical growth of ZnO NWs on patterns of catalyst (131, 135-138) and the spatial location of patterned catalyst determines the position of ZnO NWs, which is critical for applications such as light-emitting diodes (LEDs) and field emitters (131, 147, 148). Lateral growth of ZnO NWs along a thin film pattern edge offers another approach to realize controlled lateral growth. Trench Au/Si electrodes were fabricated and NWs grew from the sidewall of Au layer to bridge trenched electrodes (149). ZnO patterns (150, 151) or nanoparticles (152) have been deposited to realize the horizontal growth of those catalyst-free ZnO NWs on Si substrate.
This chapter focuses on the lateral growth of ZnO nanowires from the edge of Si/Al₂O₃/Si multi-layer structure, which has potential to bridge patterned devices or for nm-scale shadow lithography. Deposition conditions of controlled temperature and O₂ pressure were found for catalyst free ZnO growth on Al₂O₃ layer only (not on Si layer), which is critical for device integration. The 2-stage growth of small nanowires (~ 10 nm in diameter) starting from pattern edge first followed by a secondary growth of base on the existing wire is observed. This mechanism differs from previous reports\(^{(153, 154)}\) of NWs having a similar structure of the tip and base segments. Kinetics study demonstrates that the growth of the NWs was controlled by surface diffusion of Zn/ZnO precursor on the thin alumina face at optimal O₂ pressure and growth temperature.

### 6.2 Experimental details

Patterned multilayer structures were deposited by sputtering and ZnO nanowires were grown by the chemical vapor deposition (CVD) in a 2-zone tube furnace with Zn metal source. The fabrication process is shown schematically in Figure 6.1. Prior to sample preparation, the Si wafer (Silicon Quest International, Inc.) was sequentially cleaned with acetone, isopropyl alcohol (IPA), deionized (DI) water and nitrogen drying. Into a photoresist window (10 μm × 10 μm or 60 μm × 60 μm), a multilayer of 20 nm of Si, 10 nm of Al₂O₃ and 20 nm of Si were sputtered, respectively, using an AJA International ATC 2000 sputtering system with a base pressure of 2×10⁻⁷ torr. Lift-off process was carried out to result in square patterns of Si 20 nm/Al₂O₃ 10 nm/Si 20 nm multilayer structures on Si wafer. The resulting 10nm thick alumina line at the pattern edge acts as
the ZnO NW growth site as diagrammed in Figure 1 and is used to minimize the resulting ZnO NW diameter.

The growth of ZnO nanowires was performed in a quartz tube furnace (2.5cm i.d.) by exposing patterned wafers to Zn vapor and O$_2$ flow at 700°C with a similar procedure as Ref.(130) (see Figure 6.2). Zn vapor pressure of ~ 5 torr, as measured by weight loss and carrier gas volume (the detailed calculation in section 6.3), was generated by heating Zinc powder (Purified, Mallinckrodt Baker LLC) to 600°C. Patterned wafers were placed 8-10 cm downstream from the Zn source. At ambient pressure, a flow of 130±2 sccm of Ar (99.9%, Scott-Gross Co., INC) was used as the carrier gas when the heater was turned on. A separate O$_2$ inlet (6 mm o.d.) was placed 2cm upstream from sample to prevent oxidation of Zn source. When the temperature of Si wafer reached 700°C, a flow of 1.0±0.03 sccm O$_2$ (99.98%, Linde Gas LLC) was introduced to form ZnO NW. Both gas flows were controlled by the MKS Instruments 1179A flow controllers and great care was taken to purge the chamber with an Ar flow to keep the metallic Zn source from being oxidized during heating.

Scanning electron microscopy (SEM) images were characterized by Hitachi S900 with field emission tip for nm-resolution and Hitachi S3200 equipped with high energy dispersive spectroscopy (EDS). High resolution transmission electron microscopy (HRTEM) images were recorded by JEOL F2010 operated at 200 keV. Preparation of TEM samples for ZnO NWs at the pattern edge required two steps as shown in Figure 6.1(c) & (d). First, Si/Al$_2$O$_3$/Si patterns were deposited on the Si/Si$_3$N$_4$ 50 nm wafer and ZnO NWs were growing using the same condition described above. Then, the backside of Si wafer was dimpled mechanically by the Gatan 656 dimple grinder and the residual Si
was removed by a mixed acid (3HNO$_3$:1HF:1HAc, volume ratio) to realize an electron transparent Si$_3$N$_4$ window under the patterned area.

6.3 Results and discussion

The optical image of Si/Al$_2$O$_3$/Si multilayer patterns is shown in Figure 6.3(a). SEM shows that many ZnO NWs grow laterally from the pattern edge in Figure 6.3(b), which is promising for shadow lithography $^{(101)}$ or integration between electrodes. Each NW is composed of a tip segment with a diameter ~ 10 nm and a base segment with a diameter ~ 22 nm in Figure 6.3(c). Previously, similar microstructures with larger diameter were reported in vertical growth processes $^{(145, 153, 154)}$. To prove that ZnO NWs were formed at pattern edges, a TEM study was employed. Sample preparation required making an electron transparent Si$_3$N$_4$ window underneath the patterned multilayer areas as diagrammed in Figure 6.1. Figure 6.4(a) shows a TEM image of a ZnO NW and the selected area electron diffraction pattern (SAED) inserted indicates a single crystalline phase. The high-resolution TEM image in Figure 6.4(b) shows a spacing of 2.55±0.07 Å between adjacent lattice planes corresponding to the distance between two (0002) crystal planes, confirming [0001] as the preferred growth direction (c-axis) for ZnO NWs.

It is important to note that ZnO growth under these conditions was seen to come only from the pattern edge where the exposed Al$_2$O$_3$ layer resided and not on the Si layer, differing from reported horizontal growth of ZnO NWs from Si substrates under different growth conditions $^{(149-152)}$. Control experiments were applied to confirm that the selective growth was on Al$_2$O$_3$ and not defects at the Si pattern edge. Samples of sputtered Si
patterns on Si wafer were fabricated and no wires were found growing along the edge of Si patterns (with native SiO\textsubscript{2} coating) in Figure 6.3(d). EDS analysis of those samples shows no Zn, indicating that no Zinc particles or Zinc silicide/silicate compounds form at the edge of Si patterns. The feed Zn source is at 600\textdegree C and growth is at 700\textdegree C, so it is not expected for elemental Zn to condense on the sample surface, but will need to react with oxygen to form a non-volatile surface species. The Al\textsubscript{2}O\textsubscript{3} appears to act as a surface for this reaction while it does not occur on Si/SiO\textsubscript{2} or on the growing ZnO wires under these conditions. To test this hypothesis the exposed area of Al\textsubscript{2}O\textsubscript{3} was doubled by producing a thicker Si/Al\textsubscript{2}O\textsubscript{3} 20 nm/Si multilayer structure followed by 30 min growth ZnO at the same conditions. The ZnO volume density, calculated from NWs along the pattern edge with a scale of 1 \(\mu\)m, is \(\sim 2.2\times10^{-20}\ \text{m}^3\), which nearly doubles the ZnO volume density \(\sim 1.0\times10^{-20}\ \text{m}^3\) of Si/Al\textsubscript{2}O\textsubscript{3} 10 nm/Si samples in Figure 6.3(b). It is important to note that the initial/tip diameter of ZnO NWs remained 10nm and was not set by the thickness of the catalytic layer (20nm) as had been seen in CNT growth\textsuperscript{(127)}.

The CVD growth conditions are critical for the morphology control of ZnO NWs. Zn vapor pressure of \(\sim 5\) torr is calculated by weight loss of Zn powder and carrier gas volume. In Figure 6.2, Zn source was first heated to 600 \textdegree C very quickly by heater 1. The sample was heated to 700\textdegree C by heater 2. Pure Ar gas was filled in the chamber to prevent the chemical reaction of Zn source with O\textsubscript{2}. Then, an O\textsubscript{2} flow was introduced to the chamber for ZnO NWs growth. The time gap from the start of heater 1 to the O\textsubscript{2} flow is about 16 min. The experiment of 5 min reaction is used as an example for Zn vapor pressure calculation.
The total weight loss of Zn powder is 16.4 mg. The weight loss of Zn powder per second:

\[ \frac{16.4 \text{ mg}}{(16 \text{ min} + 5\text{ min}) \times 60 \text{ s/min}} = 1.3 \times 10^{-5} \text{ g/s}. \]

Therefore, the Zn amount loss rate:

\[ n = \frac{(1.3 \times 10^{-5} \text{ g/s})}{(65 \text{ g/mol})} = 2.0 \times 10^{-7} \text{ mol/s}. \]

The carrier gas volume:

\[ V = 130 \text{ sccm} = 2.17 \times 10^{-6} \text{ m}^3/\text{s}. \]

The temperature of ZnO source is 873 K. Therefore,

\[
P = \frac{nRT}{V} = \frac{2.0 \times 10^{-7} \text{ g/s} \times 8.31 \text{ J mol}^{-1} \text{K}^{-1} \times 873 \text{ K}}{2.17 \times 10^{-6} \text{ m}^3 \text{s}^{-1}} = 668 \text{ Pa} \approx 5 \text{ Torr} \quad (6.1)
\]

The O\(_2\) partial pressure with a flow rate of 1 sccm is \((1 \text{ sccm/130 sccm}) \times 760 \text{ Torr} \approx 5.8\) Torr.

Experiment results show that the tip and base segments dominate NWs’ structure when a sufficient O\(_2\) is supplied (\(\sim 5.8\) torr partial pressure at a flow rate \(\sim 1\) sccm). No growth of ZnO NWs was found when the O\(_2\) flow was zero. A few conical-shaped NWs were found at the pattern edge with a low O\(_2\) pressure of \(\sim 0.5\) torr, as shown in Figure 6.3(e).

When an excessive O\(_2\) is provided, e.g., O\(_2\) pressure \(\sim 50\) torr, there is uncontrolled growth of ZnO and tetrapod-shaped NWs grow both on alumina and silicon as shown in Figure 6.3(f). Similar structures had been reported in O\(_2\) rich concentration (130, 155-158) during ZnO growth. Reaction temperature is another parameter affecting the growth of ZnO NWs. At growth temperatures of 675°C, 700°C, 725°C and 800°C and reaction time of 10 min, NWs with a length of 469 ± 54 nm, 1118 ± 86 nm, 778 ± 135 nm and 244 ± 41 nm, respectively were obtained. Large ZnO particles appeared when samples were heated over 725°C consuming Zn/ZnO source and resulting in short ZnO NWs at 800°C.

To study the growth mechanism, a kinetic study with samples of different reaction times (0, 0.5, 1.25, 2.5, 5, 10 and 30 min) were prepared. All of the diameter and length data is
calculated statistically by 30 NWs selected randomly in each sample. Figure 6.5(a) shows the diameter variation of the tip and base segments grown in 30 min. With constant diameters of tip and base at ~ 10 nm and 22 nm, respectively, Figure 6.5(b) shows a constant linear density of ZnO NWs on Al₂O₃ surface along the pattern edge with 8~10 per μm. The summary of diameter and length distributions of ZnO NWs at 30 min is shown in Figure 6.6. The diameters of tip and base are 10±1 nm and 22±2 nm, respectively, which are consistent with the data in Figure 6.5(a). The length of base (1244±175 nm) is one order longer than that of tip (120±20 nm) and dominates the total length of NWs. The small deviation of the diameter, length and density data in Figures 6.5 and 6.6 reveals a uniform growth of ZnO NWs along the exposed Al₂O₃ line between two Si layers, including a simultaneous nucleation and a similar growth rates for most ZnO NWs, allowing for a kinetic study at periodically interrupted times.

The length of ZnO NWs as a function of time is shown in Figure 6.7(a). Growth rate vs reaction time, Figure 6.7(b), is derived from the slope at each time in Figure 5.7(a). 10nm diameter ZnO NW growth is initially fast but increases slowly after a 5 min reaction of Zn and O₂. The NWs growth rate at 1.25 min, also being the growth rate of tip segments at that time, reaches maximum at 543 nm/min, which is close to that of those ZnO NWs having a surface-diffusion induced growth at 700°C (159, 160). After this moment, base segments start to grow and stop the fast growth of tip segments since the base segments consume most of the ZnO source material before it diffuses to the tip segments. The lack of tip growth also shows that negligible Zn/ZnO intermediate surface species is formed on the ZnO NW surface in these growth conditions but requires the
Al$_2$O$_3$ surface. If small, 10nm diameter, ZnO nanowires are required, then growth time should be limited to less than 5 minutes.

Growth of ZnO NWs has been typically explained by the vapor-liquid-solid (VLS) and vapor-solid (VS) mechanisms. The ideal VLS growth rate can be calculated by equation (6.2) & (6.3)

$$J_N = \frac{P}{\sqrt{2\pi nkT}}$$

(6.2)

$$v = \frac{J_N \times m}{\rho}$$

(6.3)

where $J_N$ is the condensation rate (atoms/m$^2$s), $v$ is the growth rate (m/s), $m = 1.38\times10^{-25}$ kg is the mass of ZnO molecule, $\rho = 5.606\times10^3$ kg/m$^3$ is the density of ZnO, $P = 700$ Pa ($\sim$ 5 torr) is the pressure of Zn vapor derived from the mass loss of Zn powder and carrier gas volume, $T = 973$ K is the reaction temperature and $k$ is Boltzmann constant. The ideal VLS growth rate is about $4.3\times10^6$ nm/min, which is almost four orders of magnitude larger than the maxim experimental growth rate of 543 nm/min in Figure 6.7(b). The small experimental growth rate and no indication of catalyst tips in the catalyst-free ZnO NWs illustrate a VS growth mechanism that is limited by formation of a surface ZnO intermediate and surface diffusion on Al$_2$O$_3$ surface to the ZnO NW growth site at the NW tip or front of basal regrowth.

Under these experimental conditions, the amount of Zn/ZnO material provided by Al$_2$O$_3$ layer should be constant for each NW. At the beginning of tip growth,
\[-D_{Al2O3} \frac{\partial C}{\partial x} \cdot d \cdot \delta = \frac{dl_{t1}}{dt} \cdot \left( \frac{\pi \cdot r_{t}^2}{M} \right) \rho \]

(6.4)

and at the beginning of base growth,

\[-D_{Al2O3} \frac{\partial C}{\partial x} \cdot d \cdot \delta = \frac{dl_{b}}{dt} \cdot \left( \frac{\pi \cdot r_{b}^2}{M} - \frac{\pi \cdot r_{t}^2}{M} \right) \rho + \frac{dl_{t2}}{dt} \cdot \left( \frac{\pi \cdot r_{t}^2}{M} \right) \rho \]

(6.5)

So the ratio of eqn (6.5)/(6.4) results in

\[\frac{dl_{t1}}{dt} = \frac{dl_{b}}{dt} \cdot \frac{r_{b}^2 - r_{t}^2}{r_{t}^2} + \frac{dl_{t2}}{dt} \]

(6.6)

where \(C\) is the concentration of Zn/ZnO on Al\(_2\)O\(_3\) surface, \(x\) is the direction along the Al\(_2\)O\(_3\) surface pointing to the ZnO NW root (as shown by the arrow in the left schematic drawing of Figure 6.8a), \(d\) is the thickness of Al\(_2\)O\(_3\) film, \(\delta\) is the thickness of Zn/ZnO molecular layer, \(r_{t}\) and \(r_{b}\) are the diameter of tip and base segments and \(l_{t}\) and \(l_{b}\) are the length of tip and base segments, respectively. The diffusion constant of Zn/ZnO on Al\(_2\)O\(_3\) surface is considered constant and defined as \(D_{Al2O3}\). As illustrated in Figure 6.7(b), \(dl_{t1}/dt\), the growth rate of tip segments before base growth, is 543 nm/min at 1.25 min; \(dl_{t2}/dt\), the growth rate of tip segments after base growth, is 233 nm/min at 2.5 min; \(dl_{b}/dt\), the growth rate of base segments, is 86 nm/min at 2.5 min. \(r_{t}\) and \(r_{b}\) are 10 nm and 22 nm, respectively. So the ratio of growth area of base segments to that of tip segments is \((22^2 - 10^2)/10^2 = 3.8\), and

\[\frac{dl_{b}}{dt} \cdot \frac{r_{b}^2 - r_{t}^2}{r_{t}^2} + \frac{dl_{t2}}{dt} = 86nm/\text{min} \times 3.8 + 233nm/\text{min} = 560nm/\text{min} \]
which is close to the experimentally observed $dl_i/dt = 543$ nm/min. This observation confirms equation (6.6) and our hypothesis that Zn/ZnO material is provided by surface Zn/ZnO intermediates on the Al$_2$O$_3$ layer for both tip and base growth.

The proposed growth mechanism of ZnO NWs and corresponding SEM images are shown in Figure 6.8. At the beginning of the reaction, Zn/ZnO precursor is formed only on the thin Al$_2$O$_3$ layer nucleating 10nm diameter ZnO NW growth. The Zn/ZnO intermediate formed on Al2O3 diffuses along the ZnO NW to the growth plane at the tip of NWs to support a continuous growth, as shown in Figure 6.8(b) at 0.5 min. At the start of the base segment growth, Zn/ZnO source is consumed at the base surface (Figure 6.8(e)), which stops a further growth of tip segments (5 min in Figure 6.8(c)). Since the ultimate length of the narrow nanowires is quite uniform, it is likely that at this critical length, the concentration at the base region reaches a nucleation point to do longer diffusion path along the wire length. Then, base segments continue to grow and cover the tip section, reducing the observed tip length as seen in Figure 6.8(d). Large crystals appear at root of NWs and consume most of the Zn/ZnO surface intermediate and cover the reactive Al$_2$O$_3$ area thus reducing ZnO NW growth rate. By 30 minutes, negligible nanowire growth is seen and the system appears to be self-limiting.

6.4 Conclusions

Lateral ZnO NWs have been successfully grown from the edge of Si/Al$_2$O$_3$/Si multilayer structure. Small, 10 nm diameter, tip segments grow first followed by the growth of base segments (>20nm) which stops the narrow tip growth. Kinetic studies show that this
two-step growth is diffusion limited and a constant Zn/ZnO flux originates from the thin exposed Al₂O₃ layer. This leads to a faster growth rate of the tip segment compared to base segment rate that is reciprocal to the ratio of their growth area. The selective growth of NWs on alumina, without any growth on silicon, is an important step in the integration of ZnO nanowires in patterned devices. These ZnO nanowires will be used as a shadow mask to form nm-scale gaps for the single molecular device fabrication in the future.
Figure 6.1. Schematic diagrams of ZnO nanowires grown from the edge of Si/Al$_2$O$_3$/Si multi-structure. (a) sputtered Si/Al$_2$O$_3$/Si multi-layer structure patterned by photolithography and liftoff, (b) ZnO nanowires growing selectively from the pattern edge, (c) growth of ZnO nanowires on Si/Si$_3$N$_4$ 50 nm substrate and (d) dimpling and etching of Si substrate to obtain the Si$_3$N$_4$ window TEM sample.
Figure 6.2. Schematic illustration of the CVD system used to grow ZnO nanowires.
Figure 6.3. (a) The optical image for patterns of Si/Al$_2$O$_3$/Si multilayer structure and SEM images for (b) selective growth of ZnO nanowires along the edge of patterns with a reaction time of 30 min, (c) the tip segment and base segment, (d) Si patterns without Al2O3 layer after the same experimental process of (b), (e) low O$_2$ flow (0.1 sccm) and (f) high O$_2$ flow (> 10 sccm).
Figure 6.4. (a) TEM image and SAED pattern of a ZnO nanowire and (b) HRTEM image of single crystalline ZnO nanowire with lattice fringes.
Figure 6.5. (a) diameter of tip and base segments (30 samples observed) and (b) nanowires density as a function of CVD growth time.
Figure 6.6. (a) diameter and (b) length distribution of tip and base segments with a reaction time of 30 min (30 samples observed for both charts).
Figure 6.7. (a) length and (b) growth rate of ZnO nanowires during the growth process. The total length is a combination of the tip and base lengths.
Figure 6.8. (a) Proposed growth mechanism of ZnO nanowires and SEM images of ZnO nanowires with a reaction time of (b) 0.5 min, (c) 5 min and (d) 10 min; (e) SEM image of the base surface.
Chapter 7

Conclusions and future work

7.1 Conclusions

7.1.1 Molecular devices based on Au/SAM/Al₂O₃/Au structures

Au tunnel junctions of Al/Au/SAM/Al₂O₃/Au structures were fabricated successfully by atomic layer deposition (ALD) of Al₂O₃ onto HSCH₂CH₂OH self-assembled monolayer (SAM) on an Au bottom electrode. The ALD technique and HSCH₂CH₂OH bonding layer were both first used to fabricate Au tunnel junctions. The -OH terminated SAM acts to grow a conformal monolayer of Al₂O₃ from trimethyl aluminum. The nano-gaps formed at the exposed edge of Au/SAM/Al₂O₃/Au structure can be as thin as 20 Å with a barrier height of ~ 1.2 eV, which makes them excellent candidates for molecular conduction studies. One to three orders of magnitude reduction in background tunnel current density were observed compared to related junctions enabling higher performance molecular junctions. Two different molecules were applied to bridge the nano-gap electrodes formed at the edge of Au/SAM/Al₂O₃/Au structures. Control experiments confirm the current passing through attached molecules. Low temperature study shows the molecular current generated by a tunneling mechanism.

7.1.2 Photovoltaic detector based on Au/Al₂O₃/Au structures
CuPc thin films were successfully deposited between Au electrodes with a gap distance smaller than the CuPc exciton diffusion length. The 10 nm-gap photocurrent of CuPc film is over 10 times larger than 20 nm-gap photocurrent and over 50 times larger than 100 nm-gap photocurrent. This large photocurrent enhancement is the result of the nano-gap’s size being shorter than the CuPc exciton diffusion length thereby minimizing the recombination of electron-hole pairs. The large Schottky barrier contact resistance between the small area top Au electrode and the CuPc film is responsible for the diode \( I-V \) characteristics of devices in this work and is the primary limiter of efficiency.

7.1.3 Selective ZnO nanowire growth on Si/Al\(_2\)O\(_3\)/Si structures

Lateral ZnO NWs were successfully grown from the edge of Si/Al\(_2\)O\(_3\)/Si multi-layer structures. Small, 10 nm diameter, tip segments grow first followed by the growth of base segments (>20nm) which stops the narrow tip growth. Kinetic studies show that this two-step growth is diffusion limited and a constant Zn/ZnO flux originates from the thin exposed Al\(_2\)O\(_3\) layer. This leads to a faster growth rate of the tip segment compared to base segment rate that is reciprocal to the ratio of their growth area. The selective growth of NWs on alumina, without any growth on silicon, is an important step in the integration of ZnO nanowires in patterned devices. These ZnO nanowires will be used as a shadow mask to form nm-scale gaps for the single molecular device fabrication in future.

7.2 Future work

7.2.1 Single molecular device
ZnO nanowire diameters are as small as 10 nm and are thus a very good candidate as the shadow mask to cast a nanoscale gap. Our group has generated nm-scale gaps in line-of-site depositions successfully by carbon nanotubes (CNTs)\(^\text{101, 127, 128}\). Using the same technique, a 2 nm wide pattern can be casted on the edge of the Au/SAM/Al\(_2\)O\(_3\)/Au structure. Then, a single molecule can be electrically isolated in this shadow to bridge both Au electrodes, as shown in Figure 7.1.

7.2.2 Solar cells based on Metal I/Al\(_2\)O\(_3\)/Metal II multilayer structures

The Au/Al\(_2\)O\(_3\)/Au/Ti/TiO\(_2\)/CuPc device discussed in Chapter 5 is a photodetector. If the top Au electrode is replaced by an Aluminum electrode, this device becomes a solar cell, as seen in Figure 7.2. The Ti/TiO\(_2\) cap layers are removed to increase the efficiency of the new Au 50 nm/Al\(_2\)O\(_3\) 10 nm/Al 20 nm/CuPc 70 nm photovoltaic device. The work function between Au (5.1~5.4 eV) and Al (4.1~4.3 eV) is about 1 eV. Therefore, the internal electric field generated by Au and Al electrodes is similar as the electric field generated by an applied voltage of 1 V. The photocurrent is \(~13\) nA at 1 V for Au 50 nm/Al\(_2\)O\(_3\) 10 nm/Al 20 nm/CuPc 70 nm sample in a incident light intensity of 15.8 mW/cm\(^2\). Therefore, the generated photopower is \(1.3\times10^{-8}\) W. In Figure 5.2a, the distance between two top electrodes is 150 μm and the light power is 150 μm × 1000 μm × 15.8 mW/cm\(^2\) = 2.4×10\(^{-5}\) W. Therefore, the photovoltaic efficiency of the solar cell should be only \(~0.05\)%. But if the distance between two top electrodes decreases to 100 nm and the width of each top electrodes decrease to 50 nm, as shown in Figure 7.2, the photovoltaic efficiency of the new solar cells could reach 75%, which is much higher than the highest organic solar cell efficiency of \(~7\)%.

Although the calculation above is only a rough
evaluation, it is still very promising to fabricate Au 50 nm/Al₂O₃ 10 nm/Al 20 nm/CuPc 70 nm solar cells with a high power efficiency. The most challenges are protecting the top Al layer from oxidation before CuPc deposition and keeping all tunnel junctions working.

The small amount of active material between nano-gap electrodes will limit the absorption capacity. Several multilayers of Au/Al₂O₃/Al are built in Figure 7.3 to increase the absorption capacity. The large work function difference of ~ 1 eV between Au and Al can set up a high internal electric field reaching 10⁸ V/m to separate electrons and holes effectively. And no ITO material is required. Considering these benefits, solar cells made of this new designed unit in Figure 8 is very promising.
Figure 7.1. Schematic drawing of a single molecular device by a Au/SAM/Al₂O₃/Au structure.
Figure 7.2. Schematic drawing of a solar cell of Au/Al$_2$O$_3$/Al/CuPc structures.
Figure 7.3. Schematic side view of the designed solar cell unit based on Au/Al$_2$O$_3$/Al multi-stacks.
References

31. J. R. Reimers, L. E. Hall, M. J. Crossley and N. S. Hush, "Rigid fused oligoporphyrins as potential versatile molecular wires. 2. B3LYP and SCF calculated
66. J. G. Simmons, "Generalized Formula for Electric Tunnel Effect between Similar Electrodes Separated by a Thin Insulating Film," J Appl Phys 34(6), 1793-1799 (1963)
142. J. F. Conley, L. Stecker and Y. Ono, "Directed assembly of ZnO nanowires on a Si substrate without a metal catalyst using a patterned ZnO seed layer," Nanotechnology 16(2), 292-296 (2005)
155. S. N. Cha, B. G. Song, J. E. Jung, J. E. Jung, I. T. Han, J. H. Ha, J. P. Hong, D. J. Kang and J. M. Kim, "Controlled growth of vertically aligned ZnO nanowires with different crystal orientation of the ZnO seed layer," Nanotechnology 19(23), - (2008)

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Publications

1. Bing Hu, Xin Zhan, Jingyuan Yao, Bruce J. Hinds, “Molecular transport at the exposed edge of Au/SAM/Al₂O₃/Au tunnel junctions”, preparing.


